## IN-DEPTH SURVEY REPORT

CONTROL TECHNOLOGY FOR GALLIUM ARSENIDE PROCESSING

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M/A-COM Lowell, Massachusetts

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## I INTRODUCTION

The National Institute for Occupational Safety and Health (NIOSH) is the primary federal agency engaged in occupational safety and health research Located in the Department of Health and Human Services (formerly DHEW), it was established by the Occupational Safety and Health Act of 1970. This legislation mandated NIOSH to conduct a number of research and education programs separate from the standard setting and enforcement functions carried out by the Occupational Safety and Health Administration (OSHA) in the Department of Labor. An important area of NIOSH research deals with methods for controlling occupational exposure to potential chemical and physical hazards. The Engineering Control Technology Branch (ECTB) of the Division of Physical Sciences and Engineering has been given the lead within NIOSH to study the engineering aspects of health hazard prevention and control

Since 1976, ECTB has conducted a number of assessments of health hazard control technology on the basis of industry, common industrial process, or specific control techniques. Examples of these completed studies include the foundry industry, metal plating and spray painting operations, and HEPA-filtered vacuum enclosures used in the servicing of asbestos-type brakes. The objective of each of these studies has been to document and evaluate effective control techniques for potential health hazards in the industry or process of interest, and to create a more general awareness of the need for or availability of an effective system of hazard control measures.

These studies involve a number of steps or phases. Initially, a series of walk-through surveys is conducted to select plants or processes with effective and potentially transferable control concepts or techniques. In-depth surveys are then conducted to determine both the control parameters and the effectiveness of these controls. The reports from these in-depth surveys are used as a basis for preparing technical reports and journal articles on effective hazard control measures. Ultimately, the information from these research activities contribute to the data base of publicly available information on hazard control techniques for use by health professionals who are responsible for preventing occupational illness and injury

This research study of control technology for gallium arsenide processing was prompted by a growing interest in silicon alternatives for the semiconductor industry. For years, silicon had been the primary semiconductor material for integrated circuits. However, demands for higher speed devices for communication and military purposes led to a surge in the development and use of gallium arsenide technology. Gallium arsenide provides higher electron speeds, lower power consumption, and higher radiation resistivity than silicon. Because of the increased demands for gallium arsenide, it will be useful to know if different or additional hazard controls are needed in comparison to silicon-based processes. For instance, arsenic is considered to be a human carcinogen. It is used as a raw material in the gallium arsenide production process and, therefore, gallium arsenide workers may be directly exposed to it. Arsenic also may dissociate from inhaled gallium arsenide within the body.

## II PLANT AND PROCESS DESCRIPTION

## FACILITY DESCRIPTION

M/A-COM produces gallium arsenide wafers, field-effect transistors, and monolithic microwave integrated circuits. They grow gallium arsenide crystals by the Liquid Encapsulated Czochralski (LEC) technique. The floor plans of the process areas evaluated in the NIOSH in-depth survey study are presented in Figures 1 and 2. M/A-COM constructed this building specifically for gallium arsenide production which began in 1984. At the time of the study, there were approximately 160 workers.

## PROCESS DESCRIPTION

## Process Flow

For the <u>LEC crystal growth process</u>, the gallium and arsenic are loaded into a pyrolytic boron nitride crucible which is contained within a nitrogen-purged control box. The crucible is carried to the crystal puller and placed in the crucible wall support. The gallium and arsenic are melted at high temperature and high pressure in the presence of boron oxide. The boron oxide floats on the melt and serves as a liquid encapsulant to prevent the arsenic from escaping. The melt chamber is pressurized with argon. A seed crystal is lowered into the melt in the crystal puller and the desired gallium arsenide crystal ingot is grown. The LEC technique produces undoped, semi-insulating gallium arsenide ingots.

The crystal orientation of the ingot is established and then one side of the ingot is ground flat on a surface grinding machine to mark this orientation. The gallium arsenide wafers are slowly sliced from the ingot using automated saws. The waste (consisting of butts, cones, and slurries) is recovered and sold to gallium producers for reclamation of the gallium. Finally, the wafers are lapped to uniform thickness, polished, and cleaned. Other processing steps include epitaxial growth, ion implantation, photolithography, etching, metallization, wafer thinning, wafer scribing, and packaging.

In order to achieve the desired electrical properties, M/A-COM employs the vapor phase epitaxial process to grow thin layers of gallium arsenide on top of Arsenic trichloride, the arsenic source, is received in scaled glass ampoules packed in diatomaceous earth. About once every two months, the arsenic trichloride is added to the epitaxial reactor which is enclosed entirely in an exhausted hood During operation, hydrogen and silane gas dopant are metered into the epitaxial reactor. A portion of the hydrogen is directed over the arsenic trichloride liquid to entrain it into the reactor as a vapor in the hydrogen gas. The reaction chamber is surrounded by a furnace which heats the arsenic trichloride, a polycrystalline gallium arsenide source, and the gallium arsenide wafers. In the presence of hydrogen, the arsenic trichloride reacts with the polycrystalline gallium arsenide source to produce the volatile species of gallium chloride, arsenic (IV), hydrogen chloride, and smaller quantities of gallium trichloride and arsenic (II) The gallium chloride and the arsenic (IV) then react at the surface of the gallium arsenide wafer depositing gallium arsenide in a crystalline form The excess gases are

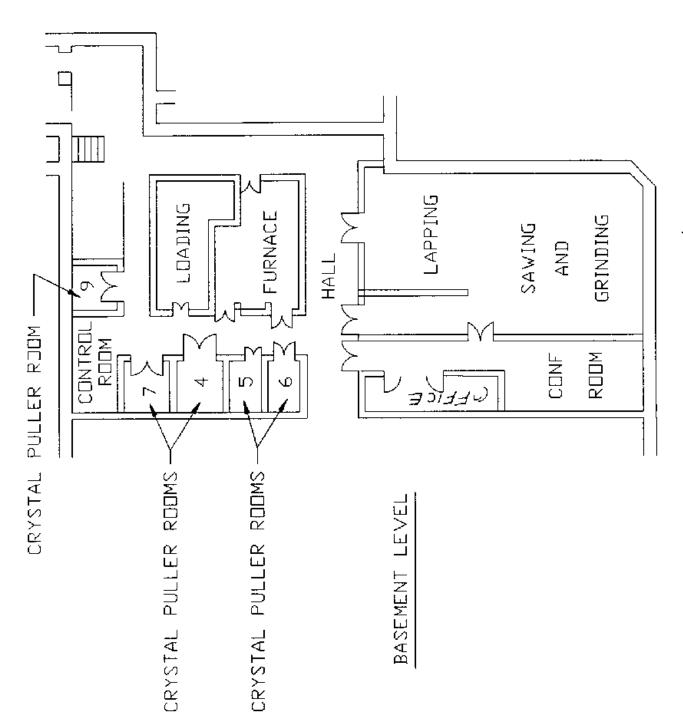


Figure 1. Plant Layout - LEC and Grinding/Sawing Areas.

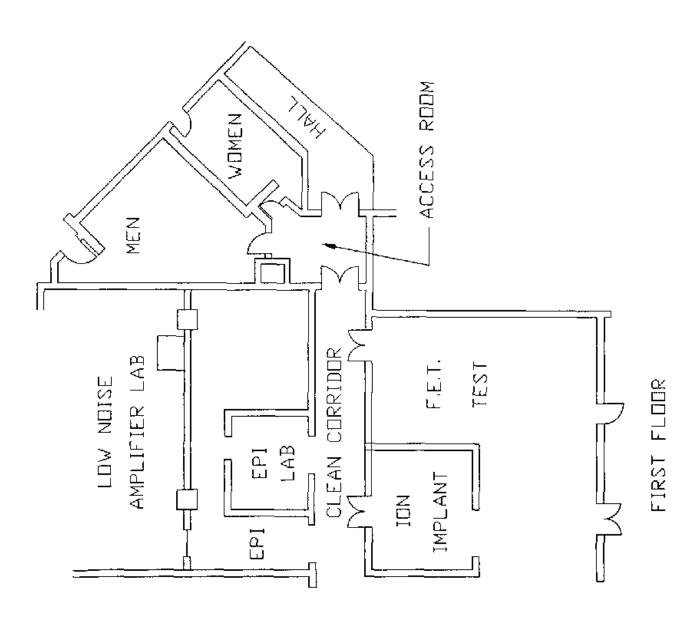


Figure 2. Plant Layout - Epitaxy and Ion Implant Areas.

condensed and the residual hydrogen is burned off as the gases exit the reaction chamber into an exhausted hood

The <u>ion implantation process</u> deposits dopants into a gallium arsenide wafer. The dopants are ionized by electrical discharge and accelerated by passing through an electric field. The beam of ions, focused on the target wafer, strikes the wafer and ions are embedded at various depths depending upon their acceleration. Silicon tetrafluoride is the gaseous dopant used at M/A-COM. The doped wafers are annealed by heating them in a dilute arsenic atmosphere furnace to relieve implantation-induced stress in the crystal lattice.

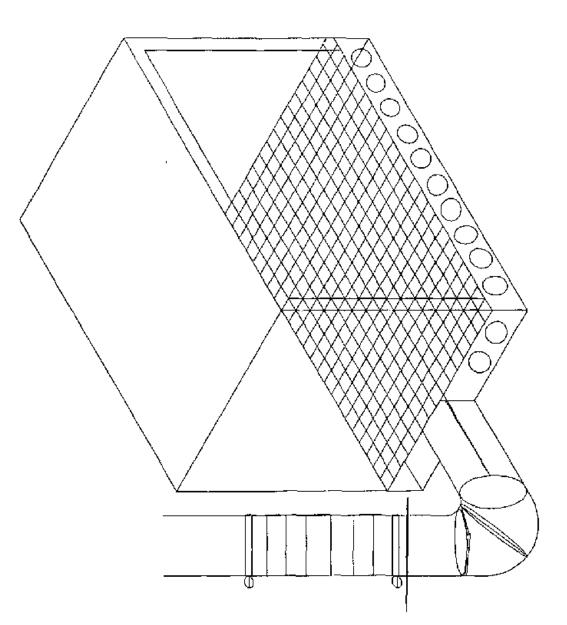
Photolithographic processes are used to transfer circuit patterns on a photographic negative (mask) to the surface of the wafer. Wet etching is also performed using hydrochloric or nitric acids and small amounts of hydrogen peroxide. For the metallization process, conductive metals such as gold, titanium, or platinum are deposited on the wafer in a vacuum. The deposited metal links the circuits on the wafer together in order for them to be functional. The wafers are then thimmed and, finally, scribed to separate the individual devices on the wafer.

## LEC Cleaning

The cleaning of the crystal puller is an integral part of the LEC process. The crystal pullers are cleaned following each production run by one or more of the LEC operators on duty. The operator dons a North or other brand full-face air-purifying respirator containing a NIOSH-approved HEPA filter, organic vapor combination cartridge. The operator also wears a disposable Tyvek® coverall with bootlets, head covering, safety glasses, and rubber gloves while cleaning. All internal surfaces of the puller are vacuumed with a HEPA-filtered vacuum cleaner and then scrubbed with a Scotch Brite® cleaning pad and isopropyl alcohol. This entire cleaning procedure is approximately a two-hour operation, performed two times per week

To clean the puller, a cart holding tools, towels, Kim Wipes<sup>®</sup>, and isopropyl alcohol is rolled into the LEC puller room. The puller is completely disassembled. Bolts are removed with an air-powered wrench and the bottom section of the puller is lowered. A Nilfisk HEPA-filtered vacuum cleaner (Model No. GS0115) is used to clean the lower section of the puller and the bottom of the upper cavity. The graphite insulation is removed and cleaned with towels and isopropyl alcohol. Each graphite piece is scrubbed with a pad containing a very fine abrasive and vacuumed (HEPA). The graphite liners are then placed in the ventilated contamination control box shown in Figure 3 (The control box, originally located on a table where it would get dirty during cleaning, was moved to a wall.)

The cleaning operator loosens the bolts to the heater, scrubs each bolt, and places them in the control box. He scrubs the heater with Norton® pads, wipes each part with Kim Wipes®, and places the parts in the control box. The Kim Wipes® and pads are placed into a hazardous waste bag for compaction.



Plexiglass Contamination Control Box

Figure 3. Ventilated Contamination Control Box Located in each LEC Puller Room.

The operator proceeds to clean the inside walls of the stainless steel puller using the pads, then vacuums the puller base, disassembles small parts of the puller base, raises the base, fastens the bolts on the base, unscrews the bolts on the top, and lowers the base. He vacuums and scrubs the seed holder and the interior of the middle sleeve The optical quartz lens is removed and taken to the laboratory The top of the puller is disassembled and the parts of the puller top that are not removed are vacuumed, scrubbed, and wiped operator leaves the puller room and manipulates the puller rods from the control panel To prevent contamination of the control area, the operator either puts a clean pair of gloves on over the old gloves or removes and disposes of his gloves as he exits the puller room. The operator returns (with a new pair of gloves if needed) and finishes scrubbing and wiping the puller The puller is reassembled The O-rings are greased and installed in the puller (The operator removes the gloves to apply the grease ) The puller, which is on a hydraulic lift, is raised at the end of cleaning to the operating height After cleaning, the LEC crystal puller is baked-out

## Process Rooms

Each crystal puller at M/A-COM is located in its own room (see Figure 1) which is under negative pressure with respect to the control panel area. Clean HEPA filtered air is provided to the control area and is pulled through the crystal growth room doors and exhausted. The air is changed in both areas at a rate of  $1\ 8$  air changes per minute

A Plexiglas® contamination control box with a nitrogen purge is employed at M/A-COM as a crucible loading station in the LEC area. The gallium and arsenic are loaded into a crucible located within the glove box. A hazardous waste barrel is provided undermoath the glove box for accidental arsenic spills. Also in the LEC production area are wet chemical stations equipped with exhaust hoods.

In the LEC process at M/A-COM, cleaning the crystal puller presented the area of greatest risk to the worker and showed the highest arsenic exposures. Therefore, an air shower system was designed and installed above the crystal puller to reduce arsenic levels. Company staff state that the air shower system is designed to move air down over the puller at a rate of 100 feet per minute. The worker stands on a grate directly underneath the air shower system while cleaning the puller. M/A-COM designed and installed this air shower system to reduce the arsenic exposure levels during cleaning. M/A-COM has designated the crystal pulling rooms as a regulated area under CFR 1910-1018.

M/A-COM also follows specific housekeeping guidelines. Mops and pails are not allowed to leave the regulated crystal pulling area. In addition, the walls and columns in the crystal pulling and epitaxy rooms are vacuumed once a month

The surface (flat) grinding machine is provided with an enclosed, wet, recirculation system with a settling tank. This system is vented to wet, packed scrubbers on the roof. The automated saws are partially enclosed and also vented to scrubbers on the roof.

The epitaxial growth operation is conducted in a clean room designed as Class 10,000, however, M/A-COM actually operates the clean rooms as Class 1,000. All of the epitaxial growth process takes place in an enclosed ventilation hood. The air in the epitaxial control room is changed at a rate of 1 3 air changes per minute, by the means of a once through air supply system. The primary purpose of the clean room is to prevent contamination of the wafers.

Both the crystal pulling area and the epitaxy laboratory are equipped with an emergency exhaust system, which the operator can activate at any time by pushing a red panic button

While in use, arsine (10 3% concentration) and silane (1,000 ppm) gases are stored in cabinets equipped with a sprinkler system and ventilated at a rate of 150 cubic feet per minute. All welded stainless steel lines are used from enclosure to enclosure for the transportation of these toxic and flammable gases.

A litmus indicator is used on the sealed arsenic trichloride ampoules for the purpose of indicating ampoule leakage or breakage

The labs have separate drains for solvent and acid/caustic wastes. The acid/caustic wastes are neutralized in an industrial waste treatment system. The solvent wastes are piped to a 1,500-gallon solvent waste storage tank. This system reduces the opportunity for chemicals to be accidentally poured into the sanitary sewers.

## EVALUATION CRITERIA

Chronic exposure to arsenic may cause malaise, fatigue, peripheral neuropathy, and perforation of the masal septum. Arsenic is also suspected of causing skin and respiratory tract cancer [1]. Stringent controls are required to assure that exposures to arsenic are less than the current OSHA permissible exposure limit (PEL) of 10  $\mu \rm g/m^3$ , the OSHA action level of 5  $\mu \rm g/m^3$ , and the NIOSH recommended exposure limit (REL) of 2  $\mu \rm g/m^3$ . The plant must establish regulated areas where inorganic arsenic exposures exceed the PEL These regulated areas must be demarcated and segregated from the rest of the workplace, access must be limited to authorized persons, and appropriate respirators must be worn [2]

The OSHA PEL for arsine is  $200~\mu\mathrm{g/m}^3$ , the NIOSH REL is  $2~\mu\mathrm{g/m}^3$ , the same as for arsenic  $^{[2,3]}$ . Arsine is an extremely toxic gas that can produce massive hemolysis and renal failure, and exposures as low as  $10~\mathrm{ppm}$  have caused coma and death. Early effects from an exposure are characterized by giddiness, headache, shivering, and abdominal pain  $^{[4]}$ . Arsine has a slight garlic odor which is only detectable above safe levels  $^{[1]}$ 

At M/A-COM, some of the solvents and gases used include methanol, fluorocarbon compounds, silane, and a very small amount of trichloroethylene (TCE) in the wafer manufacturing process. Methanol can cause optic nerve damage and blindness. However, these symptoms occur principally after oral-ingestion of methanol and rarely after inhalation. Fluorocarbon compounds can produce mild irritation to the upper respiratory tract. Mild central nervous system

depression may also occur in cases of exposure to very high concentrations of fluorocarbons. Silane is a pyrophoric gas and therefore presents a fire and explosion hazard  $^{[4]}$ . Acute exposure to TCE depresses the central nervous system and produces such symptoms as headache, dizziness, fatigue, and nausea  $^{[1]}$ . Hydrochloric and nitric acids used in etching processes can cause severe burns to the skin on contact, fumes of these acids can damage the respiratory tract. The NIOSH REL and OSHA PEL are 5,000  $\mu\text{g/m}^3$  (TWA) for HNO3. The PEL for HCl is 7,000  $\mu\text{g/m}^3$  (15-minute ceiling), there is no NIOSH REL  $^{[2,5]}$ 

## III METHODOLOGY

Air Sampling and Analysis

Personal and area samples for arsenic and gallium were collected on 37 mm diameter cellulose ester, 0.8  $\mu$ m pore size filters. Prior to the conduct of the survey, the filters were pretreated with a sodium carbonate/glycerol solution and dried by drawing a sufficient volume of air through them to minimize the initial pressure drop

Two types sampling trains were used for the collection of arsenic and gallium, as described in Table 1. One consisted simply of a treated filter and a DuPont P-4000 pump operated at a flow rate of approximately 1.5 liters per minute (Lpm). The other consisted of a treated filter in series with a charcoal tube and a DuPont P-2500 pump operated at a flow rate of approximately 0.5 Lpm. This latter was employed because in the presence of heated arsenic sources, arsenic trioxide vapors or volatilized arsenical materials may be present in the air. Vapors may pass through conventional filters, hence, monitoring with only the filter could underestimate the total arsenic exposures. The charcoal tubes consisted of 400 mg of activated coconut-based charcoal in the main section and 200 mg of activated charcoal in the backup section. A larger (400 mg/200 mg) charcoal tube was used instead of the 100 mg/50 mg charcoal tube provided for in NIOSH Method 6001<sup>[6]</sup> in order to allow the 0.5 Lpm flow rate. For personal samples, the charcoal tube was placed in a sorbent tube holder in series with a treated filter. The tube holders were pretested for leaks prior to the conduct of the survey.

Arsine vapors were collected using the same sampling train at a flow rate of approximately 0 1 Lpm using DuPont P-200 pumps. The prefilter was analyzed for arsenic and gallium

Sampling duration was based on the adsorptive capacity of the tubes for the contaminant to be sampled. Approximate full-shift samples were taken with the filter cassettes, however, the charcoal tubes were changed every 2 to 3 hours in order to avoid breakthrough. During operations that lasted only part of the shift, such as annealing, shorter (2- to 6-hour) samples were taken. Additionally, short-term sampling for arsenic and gallium was performed specifically for the duration of the LEC cleaning operation.

Air sampling was also performed for various acids. Mineral acid adsorption tubes (400 mg/200 mg) were used to sample for nitric and hydrochloric acids with DuPont P-2500 pumps at a flow rate of approximately 0.5 Lpm

Table 1. Sampling and Analytical Methods

Sample Train	Flow Rate (Lpm)	Analyte	Analytical Method <sup>[6,7]</sup>
Filter	1.5	Arsenic, Gallium	Graphite Furnace AA According to NIOSH Method 7901
Filter and Charcoal Tube	0.5	Arsenic, Gallium (filter) Arsenic (tube)	Graphite Furnace AA According to NIOSH Method 7901 (filter) Graphite Furnace AA According to NIOSH Method 6001 (tube)
Prefilter and Charcoal Tube	0.1	Arsenic, Gallium (filter) Arsenic (tube)	Graphite Furnace AA According to MIOSH Method 7901 (filter) Graphite Furnace AA According to NIOSH Method 6001 (tube)

All filter samples for arsenic and gallium were analyzed by graphite furnace atomic absorption spectrophotometry (AA) in accordance with NIOSH Method 7901 [7] The graphite furnace AA was found to be more appropriate for the desired sensitivity than the ICP method for these metals. For samples analyzed for arsenic and gallium, the limit of detection (LOD) ranged from 0.03 to 0.1  $\mu$ g/filter for arsenic and 0.02 to 0.2  $\mu$ g/filter for gallium, depending on the specific analytical batch. The limit of quantitation (LOQ) ranged from 0.08 to 0.32  $\mu$ g/filter for arsenic and 0.06 to 0.52  $\mu$ g/filter for gallium. Charcoal tubes were analyzed for arsenic by NIOSH Method 6001 [6] by means of graphite furnace AA. The LOD for the charcoal tubes ranged from 0.02 to 0.05  $\mu$ g/tube and the LOQ ranged from 0.051 to 0.13  $\mu$ g/tube for arsenic. NIOSH Method 7903 [7] was employed for the analysis of the mineral acid tubes. The LOD was 1.0  $\mu$ g/tube for hydrochloric acid and 0.5  $\mu$ g/tube for nitric acid. The LOQ was 3.6  $\mu$ g/tube for hydrochloric acid and 1.6  $\mu$ g/tube for nitric acid.

## Wipe Samples

Wipe samples were also taken to measure arsenic surface contamination. Wearing polyethylene gloves, an investigator removed a Whatman 42, 7 cm (1 8-inch) diameter filter from the box. The filter was moistened with 0 4 milliliters of triple distilled defonized water using a pipette. Areas of 100 cm² were wiped with the moistened filter. Plexiglas® templates or masking tape were employed to delineate the areas. The filter was folded in half with the exposed side in and folded again to form a 90° angle in the center of the filter. It was placed, angle first, in a clean glass vial and capped for submission to the laboratory. In order to determine the degree of variability in a measurement, side-by-side replicate wipe samples were taken for several of the initial wipes. In addition, for several samples, the same area was rewiped with another filter paper in order to determine a collection efficiency.

Wipe samples were collected in the LEC and grinding/sawing areas. These samples were analyzed by graphite furnace AA in accordance with NIOSH Method 7901  $^{(7)}$ . The LOD for arsenic was 0.08  $\mu \rm g/filter$  and the LOQ was 0.25  $\mu \rm g/filter$ 

## OBSERVATIONS

During the sampling survey, effective work practices and use of personal protective equipment were documented, especially during the LEC cleaning Ventilation measurements were taken using either a Kurz or a TSI hot-wire anemometer

IV CONTROL TECHNOLOGY

## PRINCIPLES OF CONTROL

Occupational exposures can be controlled by the application of a number of well-known principles including engineering measures, work practices, personal protection, and monitoring. These principles may be applied proximate to the hazard source, to the general workplace environment, or at the point of occupational exposure to individuals. Controls applied at the source of the hazard, including engineering measures (material substitution, process and

equipment modification, isolation or automation, local ventilation) and work practices, are generally the preferred and most effective means of control, both in terms of occupational and environmental concerns. Controls which may be applied to hazards that have escaped into the workplace environment include dilution ventilation, dust suppression, and housekeeping. Control measures may also be applied near individual workers, including the use of remote control rooms, isolation booths, supplied-air cabs, work practices, and personal protective equipment.

In general, a system comprised of the above control measures is required to provide worker protection under normal operating conditions as well as under conditions of process upset, failure, and/or maintenance. Process and workplace monitoring devices, personal exposure monitoring, and medical monitoring are important mechanisms for providing feedback concerning effectiveness of the controls in use. Ongoing monitoring and maintenance of controls to ensure proper use and operating conditions, and the education and commitment of both workers and management to occupational health are also important ingredients of an effective control system.

These principles of control apply to all situations, but their optimum application varies from case to case. The application of these principles are discussed below

## RESULTS/DISCUSSION

The parameters and analytical results of individual samples are shown in the appendices to this report

## Arsenic Air Samples

Analytical results for arsenic on 23 field blanks were all less than the LOQ and 21 were less than the LOD — Similar analyses performed on 13 charcoal tube field blanks were all below the LOD — Therefore, no blank corrections were made to the analytical results of samples collected on either the filters or the charcoal tubes

Results of personal sampling for arsenic for four gallium arsenide processes are presented in Table 2a These include LEC, LEC cleaning, grinding/sawing, and epitaxy The arithmetic and geometric mean arsenic concentrations in LEC, grinding/sawing, and epitaxy are compared in Figure 4 The average exposure during the LEC process was 0.9  $\mu g/m^3$  except during cleaning. Four of the five samples were taken on the same day shift operator during four days of sampling Arsenic exposures during LEC cleaning averaged 426  $\mu \mathrm{g/m}^3$  and ranged from 125 to 1030  $\mu g/m^3$  A typical LEC puller cleaning took 2 to 3 Three workers were sampled over two days during LEC puller cleaning One worker, who was sampled on two different days, had an average personal exposure concentration to arsenic of 150 µg/m³, a second worker had a personal exposure concentration of 380  $\mu g/m^3$ , but a third worker had an exposure of 1,030  $\mu g/m^3$  Either individual work practices or the particular puller cleaned may have contributed to this seven-fold difference in personal sample concentrations A full face (organic vapor/toxic particulate, dual cartridge) air-purifying respirator was worn during LEC cleaning

Table 2a. Personal Exposures to Total Arsenic by Process

	•	Arramara.	Arsenic Concentration*					
Area Worked	Number Sample of Duration Samples (min)		Arithmetic Mean (ug/m <sup>3</sup> )	Geometric Mean (ug/m³)	Range (ug/m³)			
LEC	5	425	0.9	0.6	0.2 - 2.1			
LEC cleaning	4	177	426	304	125 - 1030			
Grinding/Sawing	3	155	1.6	1.5	1.0 - 2.6			
Epitaxy/Annealing	4	299	< 2.4	< 2.3	<1.7 - <3.4			
OSHA PEL OSHA Action level NIOSH REL	10 uo 5 uo 2 ux	3/m <sup>2</sup>						

<sup>\*</sup> Sum of arsenic collected on filter and charcoal tubes.

Table 2b. Personal Exposures to Total Arsenic by Process

		7	Arsenic Concentration*						
Area Worked	Number of Samples	Average Sample Duration (min)	Arithmetic Mean (ug/m³)	Geometric Mean (ug/m³)	Range (ug/m³)				
LEC	0								
IEC cleaning	0								
Grinding/Sawing	1	141	4.4	4.4					
Ion Implantation	4	248	<0.1	<0.1	<0.1 - <0.2				
OSHA PEL OSHA Action Level NIOSH REL	10 uo 5 uo 2 uo	g/m²							

<sup>\*</sup> Arsenic collected on filters only.

# ARITHMETIC VS GEOMETRIC MEAN

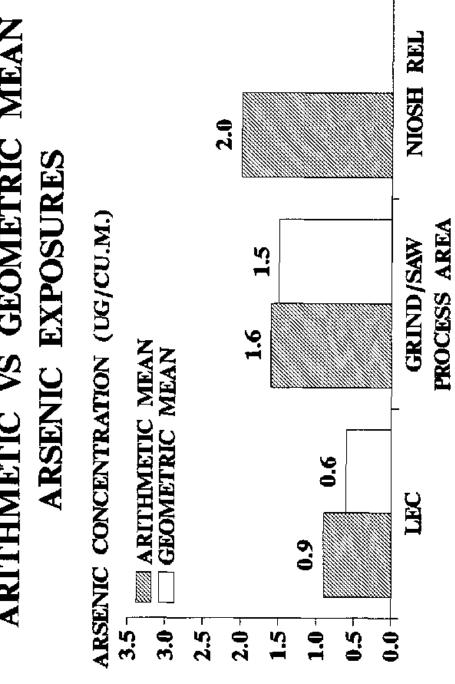


Figure 4

In the grinding/sawing area, arsenic exposures averaged 1 6  $\mu g/m^3$  and ranged from 1 0 to 2 6  $\mu g/m^3$  (Table 2a). A single personal sample for arsenic, collected on a grinding/sawing operator using a filter without a charcoal tube, was 4 4  $\mu g/m^3$  as shown in Table 2b. Thus, the overall arithmetic mean exposure for personal samples in grinding/sawing, collected using both types of sampling trains, was 2 3  $\mu g/m^3$ 

All of the personal samples for vapor phase arsenic collected in the epitaxial area were below the LOD which averaged 2 4  $\mu g/m^3$ . These results indicate that the current controls for arsine/arsenic in epitaxy most likely prevent routine exposure to airborne arsenic and arsine. Personal samples for arsenic collected on the operator for the ion implantation process using a filter only sampling train were all below the LOD which ranged from 0.1 to 0.2  $\mu g/m^3$  (Table 2b). This worker also spent considerable time in the epitaxy area which is across the hall from the ion implantation process, but within the main clean room zone.

Only during LEC cleaning were time-weighted average (TWA) personal arsenic exposures above the NIOSH REL of 2  $\mu \rm g/m^3$  and above the OSHA action level of 5 0  $\mu \rm g/m^3$ , as shown in Table 2a. Although respirators are worn during LEC cleaning, prudent practice indicates that efforts should also be made to improve engineering controls and work practices during this activity. In the grinding/sawing area, two of four personal samples were above the NIOSH REL, but all were less than the OSHA action level. Because several samples showed arsenic levels above the NIOSH REL, additional monitoring for arsenic is recommended in the sawing/grinding area.

Samples in the LEG during routine operation and in epitaxy were collected for almost a full shift (5 to 7 hours), however, sampling times during LEG cleaning and in grinding/sawing were generally under 3 hours. Cleaning an LEG puller requires about 3 hours, in grinding/sawing, workers were sampled for only a half day on the first day and were willing to wear the sampler only for half-days during the remainder of the survey

Area arsenic levels for each process area studied are shown in Tables 3a and b. The former shows results for samples collected using a filter followed by a charcoal tube, and the latter are filter only sample results. Figure 5 compares average personal arsenic concentrations (filter plus tube samples) with average area concentrations (filter plus tube samples) for the LEC, grinding/sawing, and epitaxy process areas as well as background arsenic concentrations taken in halls/offices away from the process areas. Personal concentrations were a little higher than area arsenic concentrations, however, in epitaxy the difference in average arsenic concentrations was due to a higher limit of detection for personal samples than for area samples.

Arithmetic means of arsenic sample concentrations in the LEC puller rooms were 0.3  $\mu g/m^3$  (Table 3a) and 0.2  $\mu g/m^3$  (Table 3b) indicating very low emissions of arsenic during routine LEC operation. All arsenic concentrations at the LEC control panels, which are located just outside the puller rooms, were below the LOD, which averaged 0.3  $\mu g/m^3$  (Table 3a), and below the LOD of 0.1  $\mu g/m^3$  for the filter only samples (Table 3b). Arsenic concentration in the LEC load room averaged 0.9  $\mu g/m^3$  (Table 3a) and

Table 3a. Area Sample Total Arsenic Concentrations by Process

		<del>-</del>						
		<b>_</b>	Arsenic Concentration*					
Area Worked	Number of Samples	Average Sample Duration (min)	Arithmetic Mean (ug/m³)	Geometric Mean (ug/m³)	Range (ug/m³)			
IEC Pullers Control Panel Load Room	13 4 2	412 422 176	0.3 <0.3 0.9	0.3 <0.3 0.9	0.1 - 0.5 <0.3 - <0.4 0.7 - 1.1			
IEC Cleaning Pullers Control Panel	4 3	186 202	58 <0-8	51 <0.7	26 - 107 <0.4 - <1.2			
Grinding/Sawing	4	392	1.1	1.0	<0.4 - 18			
Epitaxy/Annealing	11	346	<1.1	<0.8	<0.2 - <2.6			
Hall between gowning and clean rooms	2	411	<1.6	<1.6	<1.5 - <1.6			
Hall/office across from LEC	4	398	0.4	0.4	<0.4 - 0.6			

<sup>\*</sup> Sum of arsenic collected on filter and charcoal tubes.

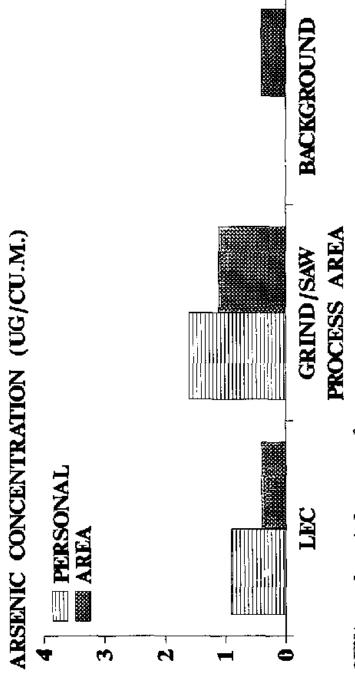
Table 3b. Area Sample Total Arsenic Concentrations by Process

	<del></del>		Arser	nic Concentrat:	ion*
Area Worked	Number of Samples	Average Sample Duration (min)	Arithmetic Mean (ug/m <sup>3</sup> )	Geometric Mean (ug/m³)	Range (ug/m <sup>3</sup> )
IEC Pullers Control Panel Load Room	12 4 2	414 422 176	0.2 <0.1 1.2	0.2 <0.1 1.0	0.1 - 0.7 <0.1 0.7 - 1.6
IEC Cleaning Pullers Control Panel Hall across from IEC	3 3 3	198 202 211	76 <0.2 <0.2	75 <0.2 <0.2	61 - 100 <0.3 <0.1 - <0.3
Grinding/Sawing	10	316	2.1	0.8	<0.1 - 7.0
Epitaxy/Annealing	1	284	<0.2	<0.2	<0.2
Ion Implantation	4	324	<0.1	<0.1	<0.1 - <0.2
Hall/office across from LEC	8	346	0.2	0.2	<0.1 - 0.4

<sup>\*</sup> Arsenic collected on filter only.

## PERSONAL VS AREA AVERAGE





\*Filter plus tube samples

1 2  $\mu$ g/m<sup>3</sup> (Table 3b) In sampling the LEC operation, each filter only sample was paired with a filter plus charcoal tube sample

Area sample arsenic concentrations in the enclosed LEG puller rooms and at the LEG control panel were slightly lower than the LEC operators' exposure during routine operation. In the LEG load room, area concentrations were comparable to the LEG operators' arsenic exposure. Area sample arsenic concentrations in the puller rooms and at the control panel were about the same as levels measured in the hall and offices across from the LEG process area. The arithmetic mean arsenic concentration in the hall/office across from the LEG area was 0.4  $\mu \mathrm{g/m}^3$  (filter and tube samples) and 0.2  $\mu \mathrm{g/m}^3$  (filter only samples)

Arithmetic means of arsenic concentrations in the grinding/sawing area were 1 1  $\mu g/m^3$  (filter plus tube) and 2 1  $\mu g/m^3$  (filter only). Higher than average concentrations were found near the operating saws, for example, two samples taken by operating saws were 4 8 and 7 0  $\mu g/m^3$ . On the other hand, the highest concentrations by the edge beveler and 0 D grinder were 0 1 and 1 3  $\mu g/m^3$ , respectively. Excluding the edge beveler results, area arsenic concentrations were nine times higher on Thursday than Monday of the survey, indicating a large variability in arsenic emissions and the potential for exposures above the OSHA action level of 5 0  $\mu g/m^3$ . Figure 6 shows the average area concentrations were higher for the saws than for the 0 D grinder and edge beveler. Average area sample concentrations were comparable to personal sample concentrations in grinding/sawing

Area samples of arsenic concentrations in the epitaxy and annealing process were all below the LOD which averaged 1 1  $\mu g/m^3$  (Table 3a). The one filter only sample for arsenic in epitaxy was less than 0 2  $\mu g/m^3$ . The LOD for arsenic for the area samples collected in epitaxy averaged about half the detection limit for the personal samples (2 4  $\mu g/m^3$ ). This is because in epitaxy all the personal samples were collected at 0 1 Lpm, while area samples were collected at both 0 1 Lpm and 0 5 Lpm

Arsenic area samples collected in ion implantation were below the LOD which averaged 0 l  $\mu \rm g/m^3$  (Table 3b), the same as the personal sampling results. Arsenic was collected on filter only samples in the ion implantation area.

Area arsenic samples collected in the hall and offices, 15 to 25 feet from the LEC and grinding/sawing process rooms, showed average concentrations of 0.4  $\mu g/m^3$  (two of the four background samples had nondetected amounts of arsenic). Doors to the LEC and grinding/sawing rooms were kept closed Because arsenic levels in the LEC and grinding/sawing areas were very low, the possibility of cross-contamination between production and nonproduction areas resulting from general airflow patterns could not be ascertained

Area samples collected in the LEC puller rooms during cleaning averaged  $58~\mu \rm g/m^3$  of arsenic (filter plus tube) and  $76~\mu \rm g/m^3$  of arsenic (filter only). The reduction in area arsenic concentrations between the puller room and control panel area during LEC cleaning was greater than 99 percent (Figure 7). Arsenic samples at the control panels during LEC cleaning were all

## AREA ARSENIC CONCENTRATIONS

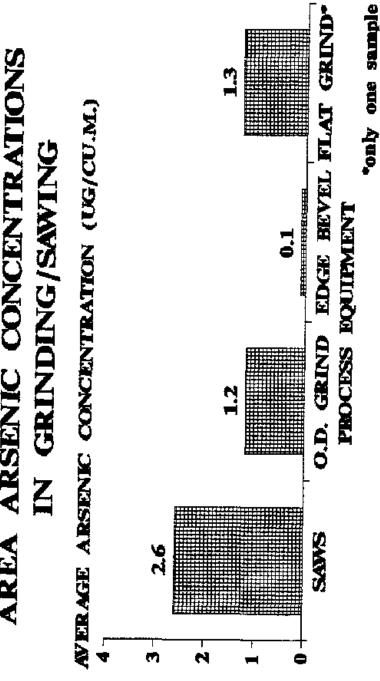


Figure 6

FILTER & TUBE DURING LEC CLEANING CONTROL PANEL ARSENIC CONCENTRATION (UG/CU.M.) 0.7 **6.8** 76

AREA ARSENIC CONCENTRATIONS

Figure 7

\*collected outside LEC area

SAMPLE LOCATION

PULLER ROOMS

HALL\*

58

- 09

75

45-

30 -

15

below the LOD, which averaged  $0.8~\mu g/m^3$  (filter plus tube), while filter only samples averaged <0 2  $\mu g/m^3$ . In the hall across from the LEC process, arsenic concentrations were below the LOD which averaged 0.2  $\mu g/m^3$ . The cleaning operator occasionally went in and out of the LEC puller room during cleaning

Area sample arsenic concentrations in the puller rooms during cleaning ranged from 26 to 107  $\mu g/m^3$  and were generally lower than the LEC cleaning operators' arsenic exposures (125 to 1,030  $\mu g/m^3$ ). Surprisingly, arsenic exposures during LEC cleaning are inversely correlated to area sample concentrations for the same pullers. For example, the LEC operator cleaning puller #7 had a personal sample concentration of 1,030  $\mu g/m^3$  (highest) and an area sample concentration of 26  $\mu g/m^3$  (lowest), while the operator cleaning puller #1 had the lowest exposure (125  $\mu g/m^3$ ) but the highest average area sample concentration (104  $\mu g/m^3$ ). Possibly, the first worker received nearly all his exposure from work practices, such as wiping and vacuuming techniques and other job tasks, while the latter workers' exposure appeared to be the result of air levels for arsenic in the puller room generated during LEC cleaning

Sample results from this survey showed that rarely did arsenic pass through the filter and collect on the charcoal tube. Arsenic was found on only 4 of the 153 charcoal tubes and ranged from 0 03 to 0 15  $\mu g$ . These samples included two personal samples in the LEC, one personal sample during LEC cleaning, and one area sample in the LEC. Two of the tubes were part of a sampling train which included detectable arsenic on the filter. The amount of arsenic on the charcoal tubes for these two samples represented 0 04 and 11 percent of the total sample (filter arsenic plus tube arsenic)

## Arsenic Wipe Samples

Wipe samples for arsenic were collected on various surfaces in the LEC and grinding/sawing areas. These sample results, in micrograms of arsenic per 100 square centimeters ( $\mu g/100~{\rm cm}^2$ ), are presented in Table 4. The highest arsenic levels were found on the exhaust duct work in the LEC puller rooms. 2,800  $\mu g/100~{\rm cm}^2$ . Arsenic surface contamination for all the other locations sampled in the LEC averaged less than 100  $\mu g/100~{\rm cm}^2$ . The lowest arsenic surface contamination (13  $\mu g/100~{\rm cm}^2$ ) in the LEC was measured on the control console, which is located outside the puller rooms

In the grinding/sawing area, the arsenic surface contamination found on the flat grinder was 300  $\mu g/100~\text{cm}^2$ , however, this is the result of only one sample. Arsenic on the 0 D grinder was 66  $\mu g/100~\text{cm}^2$ , but only 6  $\mu g/100~\text{cm}^2$  on the 0 D grinder enclosure. Arsenic surface contamination on a desk used by one of the operators was 33  $\mu g/100~\text{cm}^2$ 

Blank wipe samples collected at this plant were between the LOD and the LOQ and averaged 0 1  $\mu\mathrm{g}$ 

Table 4. Wipe Sample Results for Arsenic

<del></del>		1		<del>,</del>
Process	Sample Location	Number of Samples	Sample Area (cm²)	Arsenic Surface Contamination (ug/100 cm <sup>2</sup> )
LEC	Control console for IEC pullers	4	100	13
	Shelf next to ventilated control box (puller room)	5	100	47
	Top and side of exhaust duct work (puller rooms)	5	100	2,800
	Floor in front of LEC puller	1	100	64 (repeat 25)
	Top of load room dry box	1	100	35
	Top of bench	2	100	84
Grinding/ sawing	Front of O.D. grinder enclosure	1	100	5.6
	Front of O.D. grinder	2	100	66
	Flat grinder	1	100	300
	Workstation near saw	2	100	66
	Control panel for saw	1	100	45 (repeat 10)
	Top of desk	1	100	33

## Gallium Air Samples

Field blank results for gallium were below a LOD of 0.2  $\mu$ g/filter for 12 filters and below a LOD of 0.03  $\mu$ g/filter for 11 filters. None of the filter blanks contained detectable amounts of gallium, therefore, no blank corrections were made to air sample results for gallium

Callium air sample concentrations are presented in Appendix A, Table A-3 Personal sample gallium concentrations are summarized in Table 5 for four GaAs processes and the LEC cleaning operation. The highest average personal sample concentration during routine operations was found in the grinding/sawing area (2.5  $\mu g/m^3$ ). In the LEC area, exposures to gallium averaged 0.7  $\mu g/m^3$  and in epitaxy and ion implantation, exposures were below the average LODs of 1.2 and 0.1  $\mu g/m^3$ , respectively. Higher average exposures for gallium, by at least 2 orders of magnitude, were found during LEC cleaning (108  $\mu g/m^3$ ). There is no OSHA PEL or NIOSH REL for gallium, however, NIOSH recommends that worker exposure to gallium arsenide he controlled to the NIOSH REL for inorganic arsenic of 2  $\mu g/m^3$  (ceiling) as arsenic  $^{[2]}$ 

Area sample results for gallium are summarized in Table 6. All samples for gallium taken at the LEC control panel, in the LEC load room, and at the pullers were less than 1  $\mu g/m^3$  during routine operation. Grinding/sawing area sample concentrations averaged 2 1  $\mu g/m^3$ , the same as the personal sample concentrations for gallium in this area. In epitaxy, ion implantation, and in the halls and offices away from GaAs processing, average gallium concentrations were less than 0.6  $\mu g/m^3$ . During LEC cleaning, area gallium concentrations averaged 7  $\mu g/m^3$ , which is much lower than personal sample concentrations during LEC cleaning. As with the arsenic results, it appears that work practices such as wiping and scrubbing were the major source of gallium exposure during cleaning of the LEC pullers

The gallium moiety (i.e., the gallium portion) of gallium arsenide is 48%, therefore, an almost one to one gallium to arsenic ratio was expected for the process areas which used predominantly gallium arsenide. In all process areas sampled, except during LEC cleaning, the amount of gallium was almost the same as that of arsenic for the same filter. However, during LEC cleaning the gallium concentrations averaged only 13 percent of the arsenic concentrations indicating that the puller interior is contaminated primarily with arsenic

## Inorganic Acid Results

Field blank results for nitric acid were all below the average detection limit of 0.5  $\mu \rm g/tube$ , therefore, no blank corrections were made to air samples for this acid. Field blanks for hydrochloric acid averaged 5.0  $\mu \rm g/tube$  and the air sample results for HCl acid were appropriately blank corrected

Area samples for hydrochloric and nitric acids were collected at the LEC wet bench over a 4-day period. Average concentrations are shown in Table 7 Generally, two consecutive 4-hour samples were taken each day. Nitric acid concentrations were well below the OSHA PEL and the NIOSH REL of  $5,000~\mu\mathrm{g/m}^3$ , except during the removal of a frozen ingot from the

Table 5. Personal Exposures to Gallium by Process

			Gallium Concentration*					
Area Worked	Number of Samples	Average Sample Duration (min)	Arithmetic Mean (ug/m <sup>3</sup> )	Geometric Mean (ug/m <sup>3</sup> )	Range (ug/m³)			
LEC	5	389	0.7	0.3	<0.1 - 2.4			
LEC cleaning	4	177	108	38	9.9 -361			
Grunding/Sawing	4	152	2.5	2.3	1.6 - 4.4			
Epitaxy	4	299	<1.2 <0.9		<0.6 - <2.7			
Ion Implantation	4	232	<0.1	<0.1	<0.1 - <0.2			
OSHA PEL none NIOSH REL none								

<sup>\*</sup> Gallium collected on filters only.

Table 6. Area Sample Gallium Concentrations by Process

		Average	Gal	llıum Concentrat	:10n*
Process/Room	No. of Samples	Sample Arithmetic		Geometric Mean (ug/m³)	Range (ug/m³)
LEC Pullers Control Panel Load Room	12 8 4	413 422 176	0.2 <0.1 <0 3	0.1 <0.1 <0.2	<0.1 - 0.9 <0.3 <0.1 - <0.4
IEC cleaning Pullers Control Panel	7 6	191 202	6.8 <0.6	4.0 <0.3	0.5 - 18 <0.1 - <1.8
Hall across from LEC	3	211	<0.4	<0.4	<0.1 - <0.6
Grinding/Sawıng	14	337	2.1	1.0	<0.1 - 7.4
Epitaxy/ Annealing	12	341	<0.5	<0.3	<0.1 - 1.7
Ion Implantation	4	340	<0.1	<0.1	<0.1
Hall/office across from LEC	12	363	0.3	0.2	<0.1 - 0.5
Access room to clean area	2	411	<0.6	<0.6	<0.4 - <0.8

<sup>\*</sup> Gallium collected on filter only

Table 7. Inorganic Acid Concentrations

Table 7. Histiganto Abia Concarciacionis										
Parameter	Unit	HCl*	HNO <sub>3</sub>							
LEC Wet Bench	·									
Samples	Number	4	4							
Arithmetic mean	ug/m³	1907	960							
Std deviation	ug/m³	2800	1580							
Range: Low High	ug/m³	44 6800	7 3700							
Average sample duration	minutes	412	412							
Epitaxy Acid Cleaning		-								
Samples	Number	4	4							
Arithmetic mean	na∖w <sub>3</sub>	12	3.7							
Std deviation	ug/m³	5	0.2							
Range: Low High	ug/m³	8 18	3.4 4.0							
Average sample duration	minutes	380	380							
OSHA PEL	ug/m³	7,000 (ceiling)	5,000 (TWA)							
NTOSH REL	ug/m³		5,000 (TWA)							

<sup>\*</sup> Blank corrected.

crucible with aqua regia when the nitric acid concentration was 3,700  $\mu \rm g/m^3$  . Hydrogen chloride concentrations were 800  $\mu \rm g/m^3$  or less, except for one 4-hour sample (12,600  $\mu \rm g/m^3$ ) collected while removing a frozen ingot with aqua regia, this concentration exceeded the OSHA PEL of 7,000  $\mu \rm g/m^3$  (ceiling)—(NIOSH does not have an REL for hydrogen chloride)—Local exhaust ventilation measurements at the acid hood showed a face velocity of 60 fpm. The hydrochloric acid results indicate that the local exhaust ventilation rate at the LEC wet bench may, at times, be inadequate for the control of acid emissions such as during acid removal of a frozen GaAs ingot

In the epitaxy room, area samples for hydrogen chloride and nitric acids were collected above the acid cleaning wet station over a 4-day period. Average concentrations are shown in Table 7. Generally, two consecutive 4-hour samples were taken each day. Nitric and hydrochloric acid concentrations were 2 to 3 orders of magnitude below the OSHA PEL and the NIOSH REL indicating excellent control of these emissions at the acid cleaning station in epitaxy. The face velocities for the epitaxy acid hood averaged 100 fpm.

## Ventilation

In the LEC process area, air velocity measurements were taken in the puller rooms and at the wet bench acid hood. Supply and exhaust air volume rates for the air shower system in three of the LEC puller rooms are shown in Table 8. The air shower system was installed to help reduce arsenic exposures to the operator during LEC crystal puller cleaning. Air supplied by an overhead vent flows downward over the operator and is exhausted through a floor grate on which the operator stands. In the puller rooms, exhaust airflow rates ranged from 1,200 to 2,000 cubic feet per minute (cfm), supply air rates ranged between 2,400 and 4,700 cfm. The ratio of supply air volume to exhaust air volume ranged from 1.4 for puller #3 to 2.3 for pullers #5 and #7. The exhaust volume for the LEC wet bench/acid hood was 370 cfm which provided a face velocity of 60 feet per minute (fpm)

Ventilation rates for the flat grinder, epitaxy reactor, and epitaxy acid cleaning station are shown in Table 8. The exhaust volume for the flat grinder with the door to the hood fully open was 120 cfm. In the epitaxy area, the downdraft horizontal grill in front of the door to the epitaxy reactor exhausted at a rate of 500 cfm. The grill opening was about 22 by 30 inches. The face velocity for the acid cleaning hood in epitaxy was 120 cfm.

## WORK PRACTICES

A special work practice is employed by M/A-COM as part of the receiving procedure for gas cylinders which could be hazardous, such as hydrogen and arsine. A snoop® test is performed as the cylinders are taken off the delivery trucks, but before acceptance into the plant. If a cylinder is found leaking, it is sent back with the delivery truck. Cylinders accepted into the plant are placed in ventilated cabinets. A particular group of workers is designated to change the cylinders, whenever needed

Table 8. Ventilation Rates for Various Process Equipment

Process Location	Exhaust Air Face Velocity (f/m)	Supply Air Rate (cfm)	Exhaust Air Rate (cfm)	Notes
LEC puller 3 LEC puller 5		2400 2700	1700 1200	Downdraft Downdraft
IEC puller 7 (or 1)		4700	2000	Downdraft
LEC acid hood/wet bench	60		370	<u>_</u>
G/S flat grinder hood (door opening 3/4" x 14")	640		50	Air exhausted to 3-1/2" duct
Epitaxy reactor (exhaust grill beneath door)			500	Horizontal grill downdraft
Epitaxy acid cleaning hood	120		920	92-inch long tank

## MONITORING

M/A-COM has installed an MDA continuous 24-hour monitoring system for arsine with a sample port in the epitaxy laboratory. A continuous monitoring system for hydrogen is also employed

Additionally, M/A-COM hired a consultant for technical assistance with engineering controls and aspects of health and safety, and now employs a full-time engineer with these responsibilities. In the regulated area, personnel monitoring for arsenic is performed on a quarterly basis

## MEDICAL MONITORING

Proplacement medical examinations are conducted at M/A-COM which include a medical history, spirometry test, blood profile, and a 24-hour urine arsenic test. In addition, annual medical examinations are performed and the 24-hour urine tests are periodically given for people who work in the bulk area.

## PERSONAL PROTECTIVE EQUIPMENT

Safety goggles, Tyvek coveralls, shoe covers, and disposable gloves are worn in the crystal growth, epitaxy, and wafer fabrication areas. A full face (organic vapor/toxic particulates, dual cartridge) respirator is required during the cleaning of the crystal puller. Half face respirators are also required during the loading and maintenance of the crystal puller. In addition, supplied air breathing apparatus is required when adding the arsenic trichloride to the epitaxial reactor and when changing arsine cylinders.

## V CONCLUSIONS AND RECOMMENDATIONS

- Arsenic exposures during gallium arsenide production for routine operations are well controlled at this plant. Personal exposures during routine LEC operation were at or below the NIOSH REL of 2  $\mu$ g/m³. In grinding/sawing operations, some personal exposures to arsenic were above the NIOSH REL of 2  $\mu$ g/m³, but all were below the OSHA action level of 5  $\mu$ g/m³. Personal exposures in epitaxy were all below the LOD of the sampling and analytical method which averaged 2 4  $\mu$ g/m³, in ion implantation, all arsenic personal exposures were below the LOD which averaged 0 1  $\mu$ g/m³. Exposures in these four process areas were well below the OSHA PEL of 10  $\mu$ g/m³ for arsenic. Controls for arsenic during routine operations appear to be effective, however, a potential for arsenic levels above the PEL exists in the grinding/sawing operation
- Because personal and area arsenic concentrations were either close to or below the LOQ, comparisons were not made among the various sampling locations in the process rooms or for day to day variations in concentrations, except in the grinding/sawing room. Area concentrations in grinding/sawing were higher by the saws than at the grinders and edge bevelers. Also, arsenic concentrations were about 10 times higher on Thursday, the fourth day of the survey, than on Monday, in part because two saws were operated on Thursday and one on Monday. The high variability in arsenic concentrations in grinding/sawing could result in excessive arsenic

exposures on some days but not others, therefore, frequent or worst case monitoring for arsenic is recommended for this operation

- High levels of arsenic were found during the LEC cleaning operation Air-purifying respirators with a full mask were worn in this area during LEC reactor cleaning NIOSH maintains, that to protect against exposure to workplace carcinogens, respirators " should consist of supplied-air, full-facepiece, positive-pressure respirators equipped with an emergency self-contained breathing apparatus The following respirators are a self-contained breathing apparatus with a full facepiece operated in a pressure-demand mode, or a supplied-air respirator with a full facepiece operated in a pressure-demand mode in combination with an auxiliary self-contained breathing apparatus operated in a pressure-demand mode "[8] OSHA requirements for respiratory protection also specify the use of an air-supplied respirator if an operator's TWA arsenic exposure exceeds 1000  $\mu g/m^3$  (This is equivalent to a protection factor of 100 given the OSHA PEL of 10  $\mu$ g/m<sup>3</sup>)
- For the four LEG crystal puller cleaning operations monitored in this study, the cleaning operators' arsenic exposures varied by an order of magnitude. These differences may have occurred because some crystal pullers were more difficult to clean than others, and/or because of individual work practices among the three cleaning operators. The two arsenic exposures for the operator who cleaned two pullers, differed only by 40%, indicating the effect of differences between these two particular pullers on arsenic exposures was minor.
- The LEC cleaning operators' exposure to arsenic should be reduced by controlling emission sources during cleaning. Major potential sources of arsenic emissions include wiping the inside walls of the pullers with abrasive pads, unbolting the LEC crystal puller using an air-powered wrench, and dropping the HEPA-filter vacuum hose on the floor applying local exhaust ventilation while wiping and removing graphite liners and other internal parts, and wet wiping the contaminated section of the vacuum hose between each use should reduce emissions of arsenic practices used by M/A-COM personnel during LEC cleaning included transferring liners and internal parts of the crystal puller to a ventilated hood, isolating individual pullers, removal and disposal of gloves (or putting a clean pair of gloves on over the old gloves) when the operator exits the puller room to prevent contamination of the control area, and the use of a hydraulic lift to lower the puller for cleaning and return it to the operating height after cleaning. Isolation of the pullers in individual cells appears to protect workers in the control area and other LEC areas during puller cleaning Need less supply air or more exhaust for air shower to be effective
- 6 At M/A-COM, almost no arsenic was collected on the charcoal tubes following a filter Arsenic was found on only 2 6% of the 153 charcoal tubes. Thus, nearly all the arsenic at this plant would be collected using the traditional filter only sampling method for arsenic

- Relatively high levels of arsenic surface contamination were found on top of the exhaust duct work in the LEC puller rooms, the arsenic levels were at least an order of magnitude lower on the surfaces of the remaining areas sampled in the LEC and elsewhere. Since protective clothing is required in the puller rooms, this contamination should not increase worker exposure flowever, if the puller rooms are ever modified or dismantled, the rooms should be decontaminated first
- Sampling results for hydrochloric acid indicate that the local exhaust ventilation rate at the LEC wet bench may, at times, be inadequate for the control of acid emissions such as during acid removal of frozen GaAs ingots. Nitric and hydrochloric acid results indicate excellent control of these emissions at the acid cleaning station in epitaxy.

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## VII APPENDIX A

## LIST OF ABBREVIATIONS

A - AREA SAMPLE

ANNEA - ANNEALING PROCESS

AT - ACID TUBE

BCKGR(D) - LOCATION OUTSIDE PROCESS ROOM

CLEC - CLEANING LEC PULLERS

CONC - CONCENTRATION

CONSO(L) - CONSOLE

CT - CHARCOAL TUBE
DET - DETECTION
EPI - EPITAXY ROOM
F - AA FILTER

GS - GRINDING AND SAWING ROOM

ION - ION IMPLANTATION

LEC - LEC ROOM
LOAD R - LOAD ROOM
nd - NOT DETECTABLE
nq - NOT QUANTIFIED
P - PERSONAL SAMPLE

Table A-1 Individual Fifter and Charcoal Tube Sample Results

Dato	Sample Number	Vadia			Person/		Vohema	Det Limit	Areenic	Arsenic Conc	Det Limit	Gajlium	Gallium Cona
E	MUMOS	WHODIA	тура	Room	Loca- tion	Time (min)	Volume (liters)	Pitant	mass (ug)	(ug/m3)	шт	നമടാ (pg)	(ug/m3)
<u></u>	·	-				<u>'</u>				,,,,,			<u> </u>
06/15/87		F	P	LEC	вн	288	144 4	nq	0 03	0 21	nd	<0 04	<0.28
06/15/87	208	CT	P	LEC	вн	140	70 2	nd	<0.04	<0 57			
06/15/87		F	A.	LEC	P3	309	463 6		0 11	0 24	nd	<0.04	<0.09
06/15/87 06/15/87	5099 202	F Cĭ	A A	LEC LEC	P3 P3	309	155 3	nd	<0 03 <0 04	<0 19 <0 69	nd	<0 04	<0.26
06/15/87	202	QT .	Â	LEC	P3	115 72	57 8 36 2	nd nd	<0.04	<1 11			
06/15/87	209	CT	Ä	LEC	P3	122	613	nd	<0.04	<0.65			
D6/15/87		F	A	LEC	P5	317	15B O	па	0.04	0 25	nd	<0.04	<0.25
06/15/87	5105	F	A	LEC	P6	317	476.5	•	0 12	0 25	nd	<0.04	<0.08
06/15/87	215	CT	A	LEC	P5	73	38 8	nd	<0.04	<1 09			
06/15/87	203	CT	A	LEC	P5	123	617	nd	<0 04	<0 65			
06/15/87		CT	٨	LEC	P5	121	60 7	nd	<0 04	<0 66			
06/15/87	5098	F	A	LEC	P5CP	304	456 0	nd	<0.03	<0.07	nd	<0.04	<0.09
06/15/87		F	A	LEC	P5CP	304	152 2	nd	<0.03	<0.20	nd	<0 04	<0.26
D6/15/87	200	CT	A	LEC	P5CP	111	55 6	nd	<0.04	<0.72 <0.22			
06/15/87 06/15/87	201 219	CT CT	A A	LEC	P5CP P5CP	122 71	61 1 35 5	nd nd	<0 02 <0 02	<0 33 <0 58			
06/15/87	5100	F	Â	LEC	P9	315	472 5	nq	0 03	0.06	nd	<0.04	<0.08
06/15/87	5097	F	Ä	LEC	P9	315	158 0	nq	0 04	0 25	nd	<0.04	<0.25
06/15/87		CT	Ä	LEC	P9	120	60 2	nd	<0.04	<0.66			
06/15/87	213	CT	A	LEC	P9	71	35 6	nd	<0.04	<1 12			
06/15/87	5087	F	P	GS	CM	141	2115		0 92	4 35		0 93	4 40
06/15/87	5088	F	P	as	DD	145	72 7	nq	0.09	1 24		0 13	1 79
06/15/87		CT	P	G\$	DD	145	72 7	nd	<0.02	<0.28			
06/15/87	5076		A	GS	GS1	235	352 5		0 22	0 62		0 34	0 96
06/15/87		F	A	GS	GS2	237	118 7	nd	<0.03	<0 25	nq	0.06	0.51
06/15/87		CT	A	GS CD	G82	144	72 1	nd _a	<0.02	<0.28			
06/15/87 06/15/87	400 5079	CT F	A A	GS GS	G52 G53	93 240	46 6 360 0	nd nd	<0 02 <0 03	<0 43 <0 08	nd	<0.04	<0 11
06/15/87	5060	F	P	EPI	SM	146	14 6	nd nd	<0.03	<2 05	nd	<0.04	<2.74
06/15/87		CT	P	EPI	SM	146	14 6	nd	<0.02	<1 37		70 04	VE 14
06/15/87	5081	F	À	EPI	E1	234	23 4	nd	<0.03	<1 28	nd	<0.04	<1.71
08/15/87		CT	A	EPI	E1	234	23 4	nd	<0.02	<0.85			
06/15/87	5085	F	A	EPI	E2	247	123 6	n¢	<0.03	<0.24	nd	<0.04	<0.32
06/15/87	430	CT	A	EPI	E2	93	45 6	nd	<0.02	<0.43			
06/15/87	502	CT	A	EPI	E2	154	77 1	nd	<0 02	<0.28			
06/15/87	5082	F	P	ЮN	RB	159	238 5	nd	<0.03	<0 13	nd	<0 04	<0.17
06/15/87	5086		A	ION	CONSO	224	336 0	nd	<0.03	<0.09	nd	<0 04	<0 12
06/15/87	5078		A	BCKGRD		180	315 0	nd	<0.03	<0.10	nd	<0.04	<0.13
06/15/87	5074		A	BCKGRD		258	423 1	nd 	<0.03	<0.07	nq	0 04	0 09
06/15/87 06/15/87	5075 106		A		OFFICE OFFICE	256 138	128 3 69 1	nd nd	<0 03 <0 02	<0 23 <0 29	nd	<0 04	<0.31
06/15/87	108		Â		OFFICE	118	59 1	nd	<0.02	<0.29			
06/16/87	5042		P	LEC	BH	463	232 7		0 21	0 90	nd	<0.03	<0.13
06/16/87	225		P	LEC	вн	235	118 1	nd	<0.02	<0 17			
08/16/87	217		Р	LEC	вн	133	66 8	nd	<0.02	<0.30			
06/16/87	237		Р	LEC	вн	95	47.7	nd	<0 02	<0 42			
06/16/87	5089		A	LEC	LOAD R	173	259 5		0 42	1 62	nd	<0.04	<0.15
06/16/87	5072		A	LEC	LOAD R		867	nq	0.06	0 69	nd	<0.03	<0 35
06/16/87	229		A	LEC	LOAD R		887	nd	<0 02	<0 23	-		
06/16/87	5045		A	LEC	P1	386	193 8	nq	0.04	0 21	nd	<0.03	<0.15
06/16/87	230		Ÿ	LEC	P1	134	67 3	nd	<0.02	<0.30			
06/16/87	226		¥	LEC	P1	107	53 7 72 8	nd nd	<0 02 <0 02	<0 37 ∠0 27			
06/16/87 06/16/87	224 5091		A A	LEC	P1 P3	145 443	72 8 776 3	nd	-<0 02 0 15	<0 27 0 19	nd	<0.03	<0.04
08/16/87	5090		A	LEC	P3	443	222 3	ng	0.04	0 18	nd	<0.03	<0 13
001007	3080				, ,	-170		- 174	5 04	V ,0	414	-0 40	

Table A-1 - Contined

Date	Sample Number	Madin	Turs	Hoom	Person/ Loca+	Time	Volume	Det Limit	Arsenic mass	Arsenic Conc	Det Limit	Gallium mass	Galljum Cone
	17411111111111	Modia	1 Jpa	rivotii	tion	(min)	(litters)	Linet	(ug)	(ug/m3)	MIHH	(ug)	(ug/m3)
						1711 1 1114							
08/16/87	238	CT	A	LEC	P3	151	75 8	nd	<0.02	<0.26			
06/16/87		CT	A	LEC	P3	123	617	nd	<0.02	<0.32			
08/16/87 08/16/87	220 5077	CT	A	LEC LEC	P3 P5	169	84 8	nd	<0.02	<0.24	nd.	<0.04	<0.08
06/16/87	5046		Â	LEC	P5	441 441	661 5 220 8	ng ng	0 09 0 04	0 14 0 18	nd nd	<0.03	<0.14
08/18/87	231	CT	Â	LEC	P5	150	75 1	nd	<0.02	<0.27	riu	~0 00	~0 14
06/16/87	223		Ä	LEC	P5	122	61 1	ad	<0.02	<0.33			
08/16/87		CT	A	LEC	P5	169	84 6	nd	<0.02	< 0 24			
06/16/87	507B	F	A	LEC	P5CP	442	663 0	nd	<0.03	<0.05	nd	<0.03	<0.05
06/16/67	5044	F	A	LEC	P6CP	442	221 7	nd	<0.03	< 0 14	n <b>d</b>	<0.03	<0 14
06/16/87	239	CT	Α	LEC	P5CP	161	80 7	nd	<0.02	<0.25			
06/16/87		CT	Α	LEC	P5CP	170	85 3	nd	<0 04	<0 47			
08/18/87	216	CT	A	LEC	P5CP	111	55 7	nd	<0 02	<0.36			
06/16/87	5094	F	A	LEC	P9	440	660 0	nq	0 07	0 11	nd	<0.03	<0.05
06/16/87	5092	F CT	A	LEC	P9	440	220 4	nq	0 03	0 14	nd	<0.03	<0 14
06/16/87 06/16/87	221 233		A	LEC LEC	PØ PØ	169 151	84 7 76 7	nd 	<0 02 <0 02	<0 24 <0 26			
08/18/87	214		Â	LEC	P9	120	80 1	nd nd	<0.02	<0.28			
08/16/87	5010	F	P	68	CM	118	813	1112	0 16	2 61		0 14	2 28
06/16/87		ÇT	P	GS	CM	118	513	nd	<0.03	<0 49		•	
08/16/87	5008	F	A	G5	G51	450	675 0		22	3 26		28	4 15
06/16/87	5002	F	Α	GS	GS2	443	221 9		04	1 80		0 48	2 16
06/16/87	414	CT	A	GS	GS2	121	50 B	nd	<0.03	<0.60			
06/16/67	416	CT	A	GS	GS2	113	56 6	nd	<0.03	< 0 53			
08/16/87	417	CT	A	GS	GS2	115	57 6	nd	<0.03	<0.52			
06/16/97		СТ	A	88	G52	94	47 1	nd	<0.03	<0 64			
08/18/87	5003	F	A	GS	GS3	315	472 5	nd	<0.03	<0.08	nd	<0.03	<0.06
06/16/87 06/16/87	5011 6101	F F	A P	GB EPI	GS4	121	181 5	nd	0 24	1 32	nd	0 24	1 32
06/16/87	511	ÇT	P	EPI	SM SM	353 134	35 3 13 4	nd nd	<0.03 <0.03	<0 85 <2 24	nd	<0.03	<0.85
06/16/87		CT.	P	EP!	5M	78	78	nd	<0.03	<3.85			
06/16/87		CT	P	EPI	SM	141	14 1	nd	<0.03	<2 13			
08/16/87	5112	F	A	EPI	E2	426	213 4	nd	<0.03	<0 14	лd	<0.03	<0.14
08/16/87	500	CT	Α	EPI	E2	109	54 B	nd	<0.02	< 0.37			
06/16/87	519	CT	Α	EPI	E2	225	1127	nd	<0.02	<0.18			
06/16/87	518	CT	Α	EPI	E2	90	45 1	nd	<0.02	<0 44			
06/16/87	5107	F	A	EPI	E1	410	41 0	nd	<0.03	<0.73	nd	<0.03	<0.73
06/16/87		CT	A	EPI	E1	205	20 5	nd	<0.02	<0.98			
06/16/87	514	CT	Ą	EPI	E1	118	11.8	nd	<0.02	<1 69			
06/16/87	512		Ą	EPI	E1	85	8.5	nd	<0.02	<2 35			
06/16/87	5109		A	EPI	ANNEA	137	68 7	nd	<0.03	<0 44	nd	<0.03	<0 44
06/16/87 06/16/87	508 5110		A	EPI ION	ANNEA CONSO	137 375	68 7 562 5	nd	<0 02 <0 03	<0 29 <0 05	n.d	en 00	-0.05
06/16/87	5113		A P	ION	RB	248	372 0	nd nd	<0.03	<0.03	nd nd	<0.03	<0.05 <0.08
06/16/87	5111		À	BCKGRD		367	367	nd	<0.03	<0.82	nd	<0.03	<0.82
06/16/87	517		A	BCKGRD		171	17 1	nd	<0.03	<175	***		-W 02
08/16/87			A	BCKGRD	OFFICE	435	652 5		0 28	0 43		0.34	0 52
06/16/87	5009	F	Α	BCKGRD	OFFICE	437	219 0		0.1	0.48		0 084	0 38
06/16/87	109	CT	A	BCKGRD	OFFICE	94	47 1	nd	<0.02	<0 42			
06/16/87	107		A	BCKGRD	OFFICE	116	58 1	nd	<0.03	0 50			
06/16/87	105		A	BCKGRD		112	56 1	nd	<0.03	<0 53			
06/16/87	412		A	BCKGRD		115	57 6	πd	<0.03	<0 52			
06/16/87	5005		A	BCKGRD		335	502 5	_	0 13	0 26		0 18	0 32
06/17/87	5052		P	LEC	BH	475	238 2	nd	<0.03	<0.13	nd	<0.02	<0.08
06/17/87	234		P	LEC	BH BH	164	82 2	nd	<0.04	<0.49			
06/17/87	255	Ų)	<u>P</u>	LEC	BH	154	77 2	ad	<0.04	<0 52			

Table A-1 - Contined

<u> </u>	Sample				Person/			Det	Arseniq	Arsenia	Det	Gallium	Gallium
Date	Number	Media	Тура	Room	Loca-	<b>e</b> maT	Volume	Lunit	mass	Conc	Limit	mass	Conc
<u> </u>					tion	(min)	(inters)	<u>-</u>	(ug)	(ug/m3)		(ug)	(ug/m3)
08/17/87	248	СT	P	LEC	вн	152	76 2	nd	<0.04	<0 52			
06/17/87	5114	F	Ā	LEC	P1	485	727 6	",	0 11	0 15	nd	<0.02	<0.03
06/17/87	5048	F	Ä	LEC	P1	485	243 3	nd	<0.03	<0 12	nd	<0.02	<0.08
08/17/87	241	CT	Â	LEC	P1	158	79 3	nd	<0.04	<0.50			
06/17/87	243	CT	Ä	LEC	P1	141	70 7	nd	<0.04	<0.57			
06/17/87	245		A	LEC	P1	120	60 2	nd	< 0.04	<0.66			
06/17/87	258	СТ	A	LEC	P1	66	33 1	nd	<0.04	<1.21			
06/17/87	6050	F	Α	LEC	P5	444	686 0		0.11	0 17	nd	<0.02	<0.03
06/17/87	5051	F	A	FEC	P5	444	222 4	nd	<0.03	<0 13	nd	<0.02	<0.09
06/17/87	244	CT	A	LEC	P6	278	139 3	nd	<0.04	<0 29			
06/17/87	232	CT	A	LEC	P5	152	76 2	nd	<0.04	<0 53			
06/17/87	5049	F	A	LEC	P5CP	503	754 5	nd	<0.03	<0.04	nd	<0 02	<0 03
06/17/87	5053		A	LEC	P6CP	<i>5</i> 03	252 4	nd	<0.03	<0 12	nd	<0 02	<0.08
06/17/87		CT	A	LEC	P5CP	152	613	nd	<0.04	<0.49			
06/17/87	247	CT	A	LEC	P5CP	157	78 8	nd	<0.04	<0.51			
06/17/87	252	CT	A	LEC	P5CP	124	62 2	nd	<0.04	<0.64			
06/17/87	259	CT	Á	LEC	P5CP	60	30 1	nd	<0.04	<1 33			
06/17/87	5117	F	A	LEC	P9	481	721 5	ng	0 04	0 06	nd	<0.02	<0.03
06/17/87	5119	F	A	LEC	P9	481	241 1	กฎ	0 07	0 29	nq	0 02	0 08
06/17/87			A	LEG	P9	158	79 2	nd	<0.02	<0.25			
08/17/27			A	LEC	P9	138	69 2	nd	<0.02	<0.29			
06/17/87		CT	¥	LEC	P9	120	60 1	nd	<0.04	<0 67 -4 00			
06/17/87			Ā	LEC	P9	65	32 6	nd	<0 04 0 1	<1 23 0 98		0 16	1 67
06/17/87		F	P	G\$	CM	203	101 7 63 6	nq	<0.05	<0.79		<b>V</b> (0	1 07
06/17/87		CT CT	P	GS GC	CM CM	127 76	38 1	nd nd	<0.05	<1.31			
08/17/87 08/17/87			A	as G\$	GS1	436	654 0	110	11	1 68		19	2 91
06/17/87			A	GS	GS2	436	226 5	ng	02	0.88		0 35	1 55
06/17/87			Ä	GS	GS2	169	878	nd	<0.05	<0.57			. •••
06/17/87		CT	Ā	GS	GS2	141	73 2	nd	<0.05	<0.68			
06/17/87			A	G\$	GS2	126	65 4	nd	<0.05	<0.76			
06/17/87			Ä	GS .	GS3	256	384 0	nd	<0.03	<0.08	nd	<0.02	<0.05
06/17/87			A	G8	G85	431	648 5		1 2			12	1 86
06/17/87			P	EP!	8M	340	34 0		<0.03			<0.02	<0.59
06/17/87		ÇТ	P	EP!	SM	138	138		<0.04	<2 90			
06/17/87		CT	P	EPI	SM	105	105		<0.04	<3 81			
06/17/87		СТ	P	EPI	SM	97	97	nd	<0.04	<4 12			
06/17/87			Α	EP!	E2	471	236 0	nd	<0.08	<0.34	nd	<0.04	<0 17
06/17/87		CT	Α	EPI	E2	129	54 6	nd	<0.04	<0 62			
08/17/87		CT	A	EPI	E2	208	104 2	nd	<0.04	<0 38			
08/17/87		CT	A	든만	<b>E</b> 2	134	87 1	nd	<0.04	<0.60			
06/17/87	5020	F	A	EPI	E1	483	46 3	nd	<0.08	<1 73	nd	<0.04	<0.86
06/17/87	520	CT	A	EPI	E1	208	20 8	nd	<0.04	<1 92			
96/17/87	524	CT	Α	ĘΡΙ	E1	124	12 4	nd	<0.04	<3 23			
08/17/87	522	CT	Α	ΕPI	E1	131	13 1	nd	<0.04	<3 05			
06/17/87			A	EPI	ANNEA	284	426 9		<0.08				
08/17/87	5037	F	Α	EPI	ANNEA		68 <b>6</b>		<0.08			<0.04	<0 68
06/17/87		ÇT	Α	EP!	ANNEA		68 €		<0.05				
06/17/87			P	CLEC	AW	159	79 B		14			0.97	12 18
08/17/87		ÇT	Р	CLEC	AW	158	79 <b>6</b>		<0.02			. –	
06/17/87			P	CLEC	DA	138	69 2		71			25	381 31
06/17/87		CT	P	CLEC	DA	138	69 2		0.03			_	
06/17/87			P	CLEC	GM	237			45			57	47 91
08/17/87		CT	P	CLEC	GM	140	70 3		<0.02				
06/17/87		ÇT	Р	CLEC	GM	97	48 7		<0.02				
08/17/87	5065	F	Α	CLEC	P3	188	294 0	<u> </u>	19	61 22	<u>.                                    </u>	24	8 18

Table A-1 - Contined

	Sample	45. 4	<u> </u>		Person/			Det	Arsenic	Arsenic	Det	Gallium	Gallium
Date	Number	Media	Type	Ноот	Loca tion	Time (min)	Volume (Inters)	Limit	mass (ug)	Conc (ug/m3)	Ļımıt	mass	Cons (ug/m3)
[., <u></u>					цон	Annany	(urea el		(ug)	(adima)		(881	(ug/ma)
06/17/87	5059	F	Α	CLEC	P3	168	84 4		42	49 78		0.29	3 44
06/17/87	308	CT	Α	CLEC	P3	168	84 4	nd	<0 02	<0.24			
06/17/27	_	F	Α	CLEC	P5	248	124 4		63	50 62		0 43	3 46
06/17/87	5061	F	A	CLEC	P6	246	369 0		25	67 75	ηq	02	0 54
06/17/87		CT.	A	CLEC	P5	248	124 4	nd	<0.02	<0.18			
06/17/87	5058	F	A	CLEC	P5CP	248	369 0	nq	0 03	0.08	nd	<0.03	<0.08
06/17/87	5007	F	A	CLEC	P5CP	246	123 1	nd	<0.03	<0.24	nd	<0.03	<0 24
06/17/87	303	CT F	A	CLEC	P5CP	246	123 1	nd	<0.02	<0.16			4.50
06/17/87 06/17/87	5057 305	СТ	A	CLEC	P7 P7	146 146	73 3	- 4	19 <0.02	25 91 <0 27		0 11	1 50
06/17/87	5080	F	A	CLEC	P7CP	131	73 3 55 5	nd nd	<0.03	<0.46	nd	<0.03	<0 46
06/17/87	5056	F	A	CLEC	P7CP	131	1965	nd	<0.03	<0.15	nd	<0.03	<0 15
06/17/87	306		Ä	CLEC	PTCP	131	65 6	nd	<0.02	<0.30	IIu	CO 03	<b>40 13</b>
06/17/87	5066	F.	Ā	CLEC	BCKGR	253	379 5	nd	<01	<0.26	nd	<02	<0.53
06/17/87	5055	F	Â	CLEC	BCKGA	145	2175	nd	<0.03	<0 14	nd	<0.03	<0 14
06/17/87	5028	F	P	ION	AB	235	352 5	nd	<0.08	<0.23	nd	<0.04	<011
06/17/87	5035	F	A	ION	CONSO	307	460 5	nd	<0.08	<0.17	nd	<0 04	<0 0₽
08/17/87	5014	F	A	BCKGRD		414	B21 D	nd	<0.08	<0 13	nq	01	0 16
06/17/87	5001	F	A	BCKGRD	OFFICE	453	226 9	nd	<0.08	<0 35	nd	<0.04	<0.18
06/17/87	5006	F	A	BCKGRD		453	679 5	nd	<0.08	<0 12	nq	0.08	0 12
06/17/87	104	CT	Α	<b>BCKGRD</b>	OFFICE	165	82 8	nd	<0.05	<0.61			
06/17/87	115	CT	Α	BCKGRD	OFFICE	148	73 1	nd	<0.05	<0.68			
06/17/87	100	CT	Α	BCKGRD	OFFICE	142	71 1	nd	<0.05	<0.70			
06/18/87	5139	F	P	LEC	вн	463	232 0		0 44	1 90		0.56	2 41
06/18/87	256	CT	P	LEC	BH	172	86 2		0.08	0 66			
06/18/27	262	CT	P	LEC	₿H	154	77 2	ηđ	<0.04	<0 52			
06/16/87	278	CT	P	LEC	вн	137	68 6	nd	<0.02	<0.28			
06/18/87	5120	F	P	LEC	KO	435	218 6	Þη	<0.08	<0.37	nd	<0.04	<0 18
06/18/87	273	CT	Р	LEC	KO	180	90 5	nd	<0.02	<0 22			
06/18/87	270	ÇT	Р	LEC	ко	143	71 9		0 15	2 09			
06/18/87	283	CT	Р	LEG	КО	112	56 3	nd	<0.02	<0.36			
06/18/87	5054	F	A	LEC	LOAD R	179	208 5	nq	02	0 74	nd	<0.04	<0 15
06/18/87	5122	F	A	LEC	LOAD R	179	89 7	ηd	<0.08	<0.89	nd	<0 04	<0 45
06/18/87		CT	A	LEC	LOAD R	179	897	ηd	<0.02	<0 22			
06/18/87	5181	F	A	LEC	P3	405	607.5		0 42	0 69	nq	04	0.86
06/18/87	5†33	F	A	LEC	P3	405	203 2	nd	<0.08	<0.39	nd	<0 04	<0 20
06/16/87 06/18/87	276 287	CT	A	LEC	P3	143	717	nd	<0.03	<0 42			
06/18/87	271	CT CT	A	LEC LEC	P3 P3	140 122	70 2	nd nd	<0 03 <0 03	<0 43 <0 49			
06/18/87	5128		A	LEC	rs P5	444	612 6660		02	030	nd	<0.04	<0.08
06/18/87	5132		A	LEC	P6	444	222 3	nq nd	<01	<0.45	nd nd	<0.2	<0.90
06/18/87	272		Â	LEC	P6	162	81 1	ρη	01	1 23	110	W 2	×0 50
06/18/87	285		Ä	LEC	P5	141	70 6	nd	<0.04	<0.57			
06/18/87	279		Ä	LEC	P5	141	70 8	nd	<0.04	<0.67			
06/18/87		F.	A	LEC	P6CP	439	658 5	ad	<0.08	<0 12	nd	<0.04	<0.08
08/18/87	5121		A	LEC	P5CP	439	2199	nd	<0.08	<0.36	nd	<0.04	<0 18
08/18/87	278		A	LEC	P5CP	160	80 2	nd	<0.02	<0 25	,		-10 10
06/18/87	269		Ä	LEC	P5CP	149	74 6	nd	<0.02	<0 27			
06/18/87	261		A	LEG	P5CP	130	65 1	nd	<0 02	<0.31			
06/12/87	6127		A	LEC	P7	443	664 5	nd	<0.08	<0 12	nd	<0.04	<0.08
06/18/87	5120	F	A	LEC	P7	443	222 3	nd	<0 08	<0.36	nđ	<0.04	<0 18
06/18/87	277		A	LEC	P7	162	81 3	nd	<0.03	<0.37			
06/18/87	258		Α	LEC	P7	141	70 7	nd	<0.03	<0 42			
06/18/87	288		A	LEC	<b>P</b> 7	140	70 2	nd	<0.02	<0 28			
06/18/87	5017	F	Α	G5	GS1	371	808 4		29	4 77		3 1	5 09
06/18/87	5141	F	Α	Ģ5	GS2	450	225 4	_	0 34	1 51		0 36	1 60

Table A-1 - Contined

	Sample				Person/		<del></del>	Det	Arsenic	Arsenic	Det	Gallium	Gallium
Date	Number	Media	Тура	Room	Locu-	Time	Volum∎	Limit	mass	Conc	Limit	mass	Солс
					tion	(mtn)	(liters)		(ug)	(ug/m3)		(ug)	(ug/m3)
06/18/27	114		A	G\$	GS2	135	67 8	nd	<0.03	<0 44			
08/18/87		CT	A	gs .	G\$2	167	83.7	nd	<0 03	<0.38			
08/18/87		CT	٨	G8	GS2	14B	74 1	nd	<0.03	<0.40			
06/18/87	-	F -	A	GS	G.55	300	525 0		37	7 05		39	7 43
08/18/87		F	Þ	EPI	SM	356	35 6	nď	<0.03	<0.84	nd	<0 02	<0.56
06/18/87	534		P	EPI	SM	120	120	nd	<0.05	<4 17			
08/18/87	532		Р	EPi	5M	96	96	nd	<0.05	<5.21			
05/18/87		CT	P	EPI	SM	140	140	nd	<0 05	<3 57			
06/18/87		F	A	EPI	E2	464	227 5	nd	<0.03	<0 13	nd	<0 02	<0.09
06/18/87		CT	¥	EPI	E2	190	65 2	nd	<0.04	<0 42			
08/18/87		CT	٨	EPI	E2	141	70 B	nd	<0 04	<0.57			
06/18/87	425		A	EPI	E2	123	61 6	nd	<0.03	<0.49			
06/18/87	5031	F	A	EPI	E1	452	45 2	nd	<0 03	<0 68	nd	<0.02	<0 44
08/18/87		CT	A	EPI	E1	122	12 2	nd	<0.04	<3 28			
08/18/87		CT	A	EPI	E1	199	199	nd	<0.04	<2 01			
05/18/87		CT	A	EPi	E1	131	13 1	nd	<0 04	<3 05			
06/18/87		F	¥	EPI	ANNEA	373	18 <del>8</del> 7	nd	<0.03	<0.16	nd	<0.02	<0 11
08/18/87		CT	A	EPI	ANNEA	125	62 G	nd	<0 04	<0.64			
08/18/87		ĊT	A	EPI	ANNEA	109	54 6	nd	<0 04	<0.73			
06/18/87	421	ÇT	A	EPI	ANNEA	139	69 6	กติ	<0.04	<0 57			
06/18/87	5151	F	P	CLEC	AW	175	878		11	125 3		0 87	991
06/18/87		CT	P	CLEC	AW	175	878	nd	<0.04	<0.46			
06/18/87	5138	F	A	CLEC	P1	180	270 0		27	100 0		4 8	17 78
06/18/87		F	A	CLEC	P1	180	93 5		10	107 0		12	12 84
06/18/87	313		A	CLEC	P1	160	93 5	nđ	<0.04	<0.43			
06/18/87		F	A	CLEC	P1CP	228	342 0	nd	<0 1	<0.29	nd	<02	<0.58
08/18/87	5125		A	CLEC	P1CP	226	1142	nd	<0.1	<0 88	nd	<0.2	<1 75
06/18/87	310		A	CLEC	PICP	228	1142	ná	<0.04	<0 35			
06/18/87	5124	F	A	CLEC	BCKGR	234	3510	nd	<0.1	<0 28	nd	<0.2	<0 57
06/18/87	5040	F	P	ION	ЯB	286	429 0	រាជ	< 0 03	<0.07	nd	<0 02	<0.05
05/18/87	5038	F	A	ION	CONSO	453	679 5	រាថ	<0.03	<0.04	пđ	<0.02	<0.03
05/18/87	5038	F	A	BCKGRD	HALL	455	45 5	nd	<0.03	<0.66	nd	<0.02	<0 44
05/18/87	428	СТ	A	BCKGRD	HALL	193	193	nd	<0.04	<2 07			
08/18/87	508	CT	A	BCKGRD	HALL	138	138	nd	< 0 04	<2 90			
06/18/87	535	CT	Α	BCKGRD	HALL	124	12 4	nd	<0.04	<3 23			
08/18/87	5123	F	Α	BOXGRD	OFFICE	444	222 4	пq	0.08	0 36	nq	D 1	0.45
06/18/87	119	CT	Α	BCKGRD	OFFICE	137	68 6	nd	<0.03	<0 44			
06/16/87	110	CT	Α	BCKGAD	OFFICE	163	816	nd	<0.03	<0 37			
06/18/87	102	CT	A	BOKGRD	OFFICE	144	72 1	nd	<0.03	<0 42			
06/18/87	5134	F	Α	BCKGAD	OFFICE	450	875 0		03	0 44		0 31	0 46
08/18/87	5142	F	A	BCKGRD	HALL	246	359 0	nd	<0.08	<0 22	ng	0 08	0 22

Table A-2. Combined Filter and Charcoal Tube Arsenic Results

							Atsenic	Arsenic	Arsenic	Arsenic	Arsenic	Arsenic	Tuber
	Sample					Person/	Mass	шаѕѕ	mass	mass	mass	Conc	EIN,
Date	Number Time	Time	Volume	Type	Room	Location	(6n)	(6A)	<del>(6</del> 1)	(5n)	(6n)	(ng/m3)	Pate
		(mim)	(liters)				FILTER	TUBE #1	TUBE #2	TUBE #3	SUM		
06/15/87	5103	288	<del>1</del>	۵.	<u>띪</u>	H	003	8			003	0 21	
06/15/87	5099	308	<del>2</del> 5	∢	EC	P3	<b>€0 03</b>	8 8	8 8	\$ 8	<0.05	<0 42	
06/15/87	5096	317	159	∢	EC	P.	000	0 4	8 8	\$ \$	800	0 25	
06/15/87	5102	304	152	∢	EC	P5CP	<0.03	00 4	<b>0</b> 0000	<b>40 02</b>	90 OV	88 89	
06/15/87	5097	315	158	∢	EC	a.	004	& 42	0 49 80		9	83	
06/15/87	5088	145	ξ,	4	gs	6	000	8			0 0	1.24	
06/15/87	5084	237	119	⋖	GS	682	8	<b>40 02</b>	<0.05		\$0 \$0	<0.42	
06/15/87	5085	247	124	∢		E2	<0 03	<0 05 40 05	% 80 80 80 80 80 80 80 80 80 80 80 80 80		<0.05 0.05	<0.40	
06/15/87	5075	256	128	⋖	BCKGRD	OFFICE	00 00 00 00 00 00 00 00 00 00 00 00 00	<b>40 02</b>	00 00 00 00 00 00 00 00 00 00 00 00 00		ტ 9	66 69	
06/16/87	5042	463	233	۵	S	BH	021	% %	8 8		0.21	0.99	
06/16/87	5072	173	87	∢	EC	LOADR	900	8 8 8			0 0	690	
06/16/87	5045	386	\$	∢	EC	F	0 9	<0 05	<b>₹</b> 0 05	8 8 8	002	021	
06/16/87	5090	443	222	⋖	CEC	23	00	<0 05	<0.02	<b>₹</b> 005	00	0 18	
06/16/87	5046	4	224	∢	E E	ጺ	004	<0.02	<0.02	<0 05	0 04	0 18	
06/16/87	5044	442	222	∢	S S	PSCP	ბ გ	00 05 √0	8	<0 05	90 0>	<0.27	
06/16/87	5092	440	220	∢	E S	82	0 03	8 8 8	00 00 00 00 00 00 00 00 00 00 00 00 00	<0 05 <0 05	000	0 14	
06/16/87	5010	118	5	۵	es	<b>™</b>	0 16	8			0 16	261	
06/16/87	5005	443	222	⋖	GS GS	682	0.4	\ 03 03	<0 03	90 0V	0	. 8	
06/16/87	5109	137	89	∢	<u></u>	ANNEAL	60 83	<b>40 02</b>			ბ 8	8	
06/16/87	5112	426	213	∢	<u>.</u>	23	\$0 03	% %	Q 05	<0.02	<b>~0</b> 05	\$0 \$3	
06/16/87	5009	437	219	∢	<b>BCKGND</b>	OFFICE	0	<0 03	<0.03	00 05 00 05	01	0.46	
06/17/87	5052	475	238	۵	EC	18H	გ 8	8 8	8	<b>8</b>	80 00 00 00	& 88	
06/17/87	5048	485	243	4	CEC	£	۵ 8	60 8	6 2	00 08 00 08	% 00 08 00 08	\$0 \$	
06/17/87	5051	4 <del>4</del> 4	222	∢	EC CE	К	გ 8	\$ \$	00 80 80		<0.07	<0 31	
06/17/87	5053	503	252	4	) 	PSCP	8 8	8	8 8	\$ 90 05	00 08 00 08	<b>₹</b> 0 33	
06/17/87	5119	481	241	∢	Ë	2°	0 07	% 00 05	9 9 8	% %	0 07	0 23	
28/11/90	5021	203	102	Δ	GS.	₩ Ö	0	60 60 60	00 00 00 00		0 10	98	
06/17/87	5000	436	226	∢	gs	GS2	0.5	<0.05	\$0 \$0 \$6	გ 8	0 20	0 88	
06/17/87	5037	137	69	4	<u>.</u>	ANNEAL	00 00 00 00 00 00 00 00 00 00 00 00 00	\$0 0¥			& 55	V 88	
06/17/87	5025	471	838	4	<u></u>	E2	88 89	6 2	8 8	<b>8</b>	<0 12	<0.51	
06/17/87	5068	159	8	۵	CLEC	ΑW	<del>7</del>	<0.02			4 00	176	
06/17/87	5070	138	69	Δ	CLEC	Δ	ド	0 03			71 03	1027	0 0 0 0 0
06/17/87	5118	237	119	<u>α</u>	CLEC	ΘM	\$	<0.02	% 000 000 000		45 00	378	
06/17/87	5059	168	\$	4	CLEC	P3	4 2	<0 02			4 20	498	
06/17/87	5116	248	124	∢	CLEC	82	63	<0.02			630	506	
	1												

							Arsenic	Arsenic	Arsenic	Arsenic	Arsenic	Arsenic	Tube.
	Sample					Person/	Mass	mass	mass	mass	mass	Coric	Sum
Date	Number Time	r Tima	Volume	Type	Room	Location	(6n)	(B)	(E)	(B)	(Bn)	(ng/m3)	Patio
	ļ	(with)	(HIers)				FILTER	TUBE #1	TUBE #2	TUBE #3	SUM		
78/11/90	2067	246	123	A	CLEC	P5CP	<0.03	<0.02			& 88	<0.41	
06/17/87		146	23	<	CLEC	73	<u>ი</u>	00 00 00 00 00 00 00 00 00 00 00 00 00			1 90	25.9	
06/17/87		131	8	∢	ST CEC	P7CP	<0.03	₹0 05			\$ \$	<0.76	
28/11/80		•	227	4	BCKGHD	OFFICE	<b>€0 0</b> 9	<b>₹0 02</b>	<0.05	^ 8	60 51	<0.57	
06/18/87		463	232	a.	FC	표	0 44	0 057	<0.02	\$ \$	0.50	2 14	0 115
06/18/87	5120	435	219	α.	ρ	8	80 0∨	0 15	<0.02	<b>200</b>	0 15	69 ()	
06/18/87			6	4	S S	LOAD R	<0.03	<b>20 0</b> 2			6 5	1. 1.	
06/18/87		405	203	4	EG CEC	2	& &	<u> </u>	\$ \$	<b>00</b> 03	<b>\$</b> <b>₹</b>	<b>\$</b> 05	
06/18/87		444	222	∢	<u>일</u>	弘	8	0.1	<b>\$</b>	8 8	0.10	0 45	
06/18/87			220	<	S S	P5CP	<0.08	<b>₹0 0</b> 5	<0.02	≪005	<b>∆</b> 5	<0.45	
06/18/87			222	4	S	ь.	<0.08	<0.03	<b>₹</b> 000	<b>0</b> 0000	<b>₽</b>	<0 48	
06/18/87			225	≪	GS	<b>GS2</b>	0.34	<0.03	<003	& 69 63	<b>3</b> 5	151	
06/18/87			187	∢	굡	ANNEAL	\$0 \$0 \$3	^ 20	& 8	<b>8</b>	<0.07	<0.37	
06/18/87			227	∢	EPI	입	<0.03	<b>\$</b>	<b>8</b>	^ အ	<b>₹0 0</b> 2	83 ♥	
06/18/87			88	Ω	CLEC	ΑW	=	& \$			=	125	
06/18/87		180	93	<	CLEC	표	9	8 8			5	107	
06/18/87			114	∢	CLEC	P1CP	<b>&amp;</b>	8 8			<0.14	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
06/18/87			222	4	BCKGRD	OFFICE	800	& &	۵ 8	<b>0</b> 000	000	0 36	
06/15/87			146	a.	굡	WS.	<0 03	<b>₹</b> 0 05			გ 8	<3 42	
06/15/87			23 4	∢	<u>a</u>	<u></u>	<b>40 03</b>	<b>₹</b> 0 05			<b>\$</b>	<2 14	
06/16/87			35.3	α.	EPI	SM	<0.03	<b>~</b> 0 03	<0.03	& 80 83	8 8 9	<1 70	
06/16/87		410	410	∢	EPI	Ξ	<0.03	<0.02	<0.02	Q 00 05	<0 05 05	√ 75	
06/16/87			36.7	٨	BCKGRD	EPI	<0.03	8			90 00	չ 8	
06/17/87			8	凸	딥	WS	<0.03	\$	& 2	& \$	<0.07	<2 06	
06/17/87	5026	463	463	∢	픕	Ш	40 08 40 08	\$ \$	<u>\$</u>	8 8	\$ 5 7	<2 59	
06/18/87	5038	-	45 5	≪	BCKGRD	EPI	<0.03	<b>\$</b>	\$ 8	\$ 8	<b>40 0</b> 2	<u>^</u>	
06/18/87	5024		356	۵	EP	SM	<0.03	<b>△</b> 05	<b>40 05</b>	& &	<b>8</b>	<2.25	
06/18/87	5031		45 2	٧	<del>-</del>	E1	<0 03	<b>40 0</b>	<0 0>	& \$	<0.07	<1 55	

Table A-3 Filter Only Arsenic and Gallium Results

	Sample			Person/	Time	Volume	Det C	Arsenic	Arsenic	蓍	Gallum	Gallium	Ratio
Date	Number Type	Type	Room	Loca-	(TITLE)	(liters)	C.	mass	Cogo	Limit	Mass	Sorie	Galfrum/
				ton Totl				(Bn)	(ng/m3)		(Bn)	(ng/m3)	Arsenic
06/15/87	5103	٩	FEC	ВН	5	545				5	8	<0.74	
06/15/87	5104	⋖	LEC	P3	303	4635		0 11	0.24	ğ	<b>\$</b>	60 O>	
06/15/87	5099	∢	CEC	2	8	1653				달	\$	<0.26	
06/15/87	9609	∢	<u> </u>	P5	317	159 0				5	8	\$ \$	
06/15/87	5105	⋖	E E	Ps	317	475 5		0 12	0 25	ş	8	80 80 80 80	
06/15/87	5098	∢	EC	PSCP	88	4560	둳	8	<0.07	5	& 8	% 90 93	
06/15/87	5102	∢	EC	PSCP	ğ	152.2				달	8	% %	
06/15/87	5100	∢	Ω	6	315	4725	Ē	0	000	달	8	<0 08	
06/15/87	2097	∢	Ë	<b>6</b>	315	158 0	ā				8	0 25	
06/15/87	5087	<u>α</u>	g	₹	14	2115		0 92	4 35		0 93	4 40	1 01
06/15/87	5088	۵	SS	00	45	727					0 13	179	
06/15/87	5076	∢	88	GS1	88	352 5		0 22	0 62		98	960	1 55
06/15/87	5084	∢	S	GS2	237	1187				ጀ	800	051	
06/15/87	5079	⋖	SS	GS3	240	360 0	Ē	\$ 8	<b>₹0 08</b>	ਬੂ	8	<b>6</b> ±	
06/15/87	5080	م	픖	SM	146	146				g	\$ \$	42.74	
06/15/87	508	⋖	EPI	E	8	23.4				덜	8	7	
06/15/87	5085	∢	딥	E2	247	123 6				ş	8	<b>₹</b> 0 35	
06/15/87	5082	<b>a</b> ∟	<u>8</u>	88	159	238 5	P.	<b>8</b>	<0 13	ğ	8	<b>⇔</b> 17	
06/15/87	5086	⋖	<u>S</u>	CONSOL	224	3360	5	& 8	60 0 <del>0</del>	2	8 8	<0 12	
06/15/87	5073	⋖	BCKGHD	D HALL	8	315 0	덜	8	& 5	돧	8	& 5	
06/15/87	5075	4	BCKGRD	D OFFICE	256	128 3				Ę	8	<0 31	
06/15/87	5074	∢	BCKGRD	D OFFICE	258	423 1	2	8 8 8	<0 02	둳	\$	000	
06/16/87	5042	۵.	EC	BH	<del>4</del> 83	232 7				달	<0 03	<0 13	
06/16/87	5072	∢	S)	LOAD R	173	967				달	<u>ද</u> ස	& &	
06/16/87	5089	⋖	CEC	LOADR	173	259 5		0 42	1 62	g	8	& 5	
06/16/87	5045	∢	S E	<u>r</u>	386	1938				덜	8	0 5 5	
06/16/87	9030	⋖	ΕĒ	23	443	222 3				Þ	۵ 8	۵ 5	
06/16/87	5091	∢	FC	P3	443	775 3		0 15	0 19	덜	& 8	8	
06/16/87	5046	∢	ΕË	S.	<u>4</u>	2208				ş	& &	4100	
06/16/87	2022	∢.	LEC	£	441	5615	Ē	600	0 14	덜	<b>&amp;</b> <b>\$</b>	90 OV	
06/16/87	5078	∢	PC	P5CP	442	663 0	5	۵ 8	<b>₹0 02</b>	달	& &	& &	
06/16/87	5044	∢	S E	PSCP	442	221 7				g	<u>န</u> န	<b>8</b>	
06/16/87	5094	∢	EC	2	440	0 099	ā	200	0 1	5	& &	8	

Table A-3 - Continued

Ratio	Gallsum/	Arsenic		0 88	1.27	1 20		- 8								1 23	0 84	121										0 07	0 8	0 13	0 07	0 13		004	-
Gallrum	Canc	(ng/m3)	<0 14	2 28	4 45	2 16	90 O>	132	^ 88	& <b>4</b>	<0.73	40 T	% 00 08 09	۵ 8	<0.82	0 35	0 38	0 52	00 09 00 08	<b>୧</b>	<b>90 09</b>	60 O	<0 03	SO 03	8	0 08	60 09 VO 03	12 18	36131	47 91	3 44	8 16	0 54	3 46	<0.24
Gallium	Mass	(fn3)	<0.03	0 14	28	0 48	<0 03 <0 03	0 24	<0.00	8	<0 03	<b>00 03</b>	© 00 03	<b>₽</b>	<0.03	0 16	0 08	94	<b>₹</b> 0 05	<b>₹0 0</b> 5	<0.05 <0.05	00 00 00 00 00 00 00 00 00 00 00 00 00	<0.05	<b>20 0</b> 2	<b>₹</b> 0 05	0 05	8 8	0 97	ĸ	5.7	0 59	24	0	0 43	<0 03
Det.	timit		2				달		2	ş	달	달	g	덜	ğ				힏	달	Z	2	ጀ	ā	달	Ē	5						ᅙ		3
Arsenic	Conc.	(ng/m3)			326		90 OS	1 32					88	<b>0</b> 000		0 26		0 43		0 15			0 17	& 8			006					61 22	67 75		
Arsenic	mass	(fin)			KI KI		ბ გ	0 24					& &	00 80		0 13		0 28		0 11			0 11	<0 03			\$00					81	53		
Det.	C H	İ					БÜ						ğ	<u>p</u>										뒫			Ē								
Volume	(liters)		220 4	613	6750	2219	4725	1815	353	2 89	410	2134	3720	562 5	367	502 5	2190	652.5	238 2	727 5	2433	222 4	0 999	754 5	252 4	241	7215	79 6	69 2	1190	<u>\$</u>	2940	369.0	124 4	123 1
Time	(min)		440	118	450	443	315	121	353	137	410	426	248	375	367	335	437	435	475	485	<b>48</b> 5	4	444	503	503	481	48	159	138	237	<del>2</del> 8	<del>2</del>	246	248	246
Person/	Loca-	tion	64	Š	GS1	G\$2	GS3	GS4	SM	ANNEAL	Ē	<b>E</b> 2	88	CONSOL	D HALL	D HALL	D OFFICE	D OFFICE	ВH	<u>~</u>	<u>p</u> .	P5	S.	PSCP	PSCP	2	ድ	ΑW	DA	ВМ	2	2	Ps	P5	PSCP
	Room		CEC	gs	gs S	es es	Se	SS		딥	E	ā	<u>8</u>	<u>8</u>	BCKGRD	BCKGRD	BCKGRD	BCKGRD	CEC	CEC	띰	EC	LEC	EC	LEC	S E	LEC LEC	CLEC	CLEC	CLEC	CLEC	CLEC	CLEC	CLEC	OLEG
	Турв		¥	۵	4	∢	∢	4	۵	∢	∢	4	₫.	4	∢	∢	∢	∢	Δ	<	∢	∢	∢	∢	∢	4	4	<u>n</u>	Œ	D.	∢	4	∢	4	4
Sample	Number Type		5092	5010	5008	5002	5003	5011	5101	5109	5107	5112	5113	5110	5111	5005	5009	5004	5052	5114	5048	5051	5050	5049	5053	5119	5117	5068	5070	5118	5069	5065	5061	5116	2067
	Date		78/91/90	06/16/87	06/16/87	06/16/87	06/16/87	78/91/90	06/16/87	06/16/87	06/16/87	06/16/87	06/16/87	06/16/87	06/16/87	06/16/87	06/16/87	78/91/90	06/17/87	06/17/97	06/17/87	06/17/87	06/17/87	06/17/87	06/17/87	06/17/87	06/17/87	06/17/87	06/17/87	06/17/87	06/17/87	06/17/87	06/17/87	06/17/87	06/17/87

Table A-3 - Continued

Date         Number Type         Floor         Lose         (mm)         (thefs)         Limit         mass         Conc.         Limit         mass           08/17/87         5056         A         CLEC         P5CP         246         78.3         nq         0.08         nd         0.09         nd         0.01           08/17/87         5056         A         CLEC         P7CP         131         1965         nd         0.08         nd         0.01           08/17/87         5051         P         CLEC         P7CP         131         1965         nd         0.08         nd         0.01 <th>Sample</th> <th></th> <th></th> <th>Person/</th> <th>Time</th> <th>Vol⊔me</th> <th>Det</th> <th>Arsenic</th> <th>Arsenic</th> <th>Det.</th> <th>Galijum</th> <th>Gallium</th> <th>Ratio</th>	Sample			Person/	Time	Vol⊔me	Det	Arsenic	Arsenic	Det.	Galijum	Gallium	Ratio
Hongoon   Hong	=	Type	Room	Loca-	(min)	(itters)	ij	mass	Corre	ΕĦ	mass	Colic	Gallium/
A CLEC         P5CP         246         389 0         nq         003         008         nd         4           A CLEC         P7CP         146         73 3         nd         <015				tion				(6n)	(mg/m3)		(Bn)	(ng/m3)	Arsenic
A CLEC         P7         146         733           A CLEC         P7CP         131         1965         nd         <015         nd            P CLEC         P7CP         131         1965         nd         <003         <015         nd            P GS         CM         207         101            nd            A GS         GS2         236         334 0         nd         <003         <019         nd            A GS         GS3         256         334 0         nd         <003         <019         nd            A GS         GS3         236         334 0         nd         <003         <019         nd            A EPI         ANNEAL         284         466 0         nd         <003         <019         nd            A EPI         A EPI         463         463         352 0         nd         <010         <010         <010         <010         <010         <010         <010         <010         <010         <010         <010         <010         <010         <010         <010         <010         <010 </td <td>lω</td> <td>∢</td> <td>CLEC</td> <td>P5CP</td> <td>246</td> <td>369.0</td> <td>ը  </td> <td>0.03</td> <td>0 08</td> <td>g</td> <td>₹0 03</td> <td><b>80 0</b>&gt;</td> <td></td>	lω	∢	CLEC	P5CP	246	369.0	ը 	0.03	0 08	g	₹0 03	<b>80 0</b> >	
A CLEC         P7CP         131         1965         nd         <003         <015         nd            A CLEC         P7CP         131         656         nd         <003         <015         nd            A GS         GSS1         436         6540         11         168         nd            A GS         GSS1         436         6540         112         116         nd            A GS         GSS2         436         6465         nd         <003         <0.08         nd           A GS         GSS         431         6465         nd         <0.03         <0.09         nd           A GS         GSS         431         6465         nd         <0.03         <0.09         nd           A EPI         ENMANEAL         284         4260         nd         <0.08         <0.19         nd           A EPI         EN ANNEAL         137         686         nd         <0.08         <0.19         nd           A EPI         EN ANNEAL         137         2680         nd         <0.08         <0.19         nd           A BCKGRDD HALL         145         2715	Γ.	∢	OLEC C	P7	46	733					0 11	150	90 0
A CLEC         P7CP         131         65 6           P GS         CM         203         101 7           A GS         GS1         436         654 0         11 1 168           A GS         GS2         436         654 0         11 1 168           A GS         GS2         436         646 5         11 2 166         nd           A GS         GS3         431         646 5         nd         <003         <010         nd           A GS         GS5         431         646 5         nd         <003         <019         nd            A EPI         ANNEAL         137         686         nd         <008         <019         nd            A EPI         EA         471         256 0         nd         <0.08         <0.19         nd           A EPI         EA         471         260 0         nd         <0.08         <0.19         nd           A BCKGRD HALL         145         277 5         nd         <0.08         <0.11         nd           A BCKGRD HALL         145         277 5         nd         <0.08         <0.11         nd           A BCKGRD OFFICE         453	ထွ	∢	SE SE SE SE SE SE SE SE SE SE SE SE SE S	P7CP	131	1965	5	<0.03	<b>₹0 15</b>	5	© 0000	& 5	
P         GS         CM         203         1017         11         168           A         GS         GSL         436         6540         11         168           A         GS         GSL         436         6540         11         168           A         GS         GSL         436         6465         12         188         12           A         GS         GSL         431         6465         12         188         10           A         EPI         SM         340         340         10         <0.08         <0.19         nd           A         EPI         ANNEAL         137         686         nd         <0.08         <0.19         nd           A         EPI         ANNEAL         137         686         nd         <0.08         <0.19         nd           A         EPI         ANNEAL         137         686         nd         <0.08         <0.19         nd           A         EPI         ANNEAL         1463         1463         nd         <0.08         <0.19         nd           A         BCKGRD HALL         144         6210         nd         <0.08	Ö	<	CLEC	P7CP	131	65 <del>6</del>				g	<b>8</b>	<0.46	
A GS         GS1         436         654 0         11         168           A GS         GS2         436         226 5         11         168           A GS         GS3         226 5         34 0         nd         <0.03         <0.08         nd           A GS         GS3         431         646 5         nd         <0.03         <0.09         nd            A EPI         ANNEAL         137         68 6         nd         <0.08         <0.19         nd            A EPI         EI         463         463         nd         <0.08         <0.19         nd            A EPI         EV         471         236 0         nd         <0.08         <0.19         nd            A EPI         EV         471         236 0         nd         <0.08         <0.19         nd            A EPI         EV         463         0.04         <0.08         <0.17         nd            A BCKGRD HALL         443         2175         nd         <0.08         <0.17         nd           A BCKGRD OFFICE         453         679 5         nd         <0.08         <	Σ.	<u>a</u> .	SS	Ö	803	1017					0 16	157	
A GS         GS2         436         226 5           A GS         GS3         256         384 0         nd         <0.03         <0.08         nd            P EPI         SM         340         340         340         nd         <0.08         <0.19         nd            A EPI         ENNNEAL         284         346         nd         <0.08         <0.19         nd            A EPI         EV         TANNEAL         137         686         nd         <0.08         <0.19         nd            A EPI         EV         TANNEAL         137         686         nd         <0.08         <0.19         nd            A EPI         EV         TANNEAL         137         286         nd         <0.08         <0.19         nd            A BOKGARD HALL         145         2175         nd         <0.08         <0.14         nd            A BOKGARD HALL         145         2175         nd         <0.08         <0.14         nd           A BOKGARD HALL         144         621         nd         <0.08         <0.14         nd           A LEC <td>2</td> <td>∢</td> <td>gs</td> <td>GS1</td> <td>436</td> <td>6540</td> <td></td> <td>-</td> <td>168</td> <td></td> <td>19</td> <td>2 91</td> <td>1.73</td>	2	∢	gs	GS1	436	6540		-	168		19	2 91	1.73
A         GS         GS3         256         384 0         nd         <0.03         <0.08         nd            P         EPI         SM         340         340         340         12         186         nd            A         EPI         SM         340         340         340         nd         <0.08         <0.19         nd         <0.08         nd         <0.09         <0.09         nd         <0.09         <0.09         <0.09         <0.09         <0.0	8	∢	GS	GS2	436	226 5					0 35	<u>.</u>	
A GS         GS5         431         6465         12         186           P EPI         SM         340         340         md	N	∢	gs	GS3	256	384 0	ē	<0.03	80 O>	덜	<0.02	0 S	
P         EPI         SM         340         340         mode         color	ଯ	<	တ္သ	686	431	6465		12	1 86		12	1 86	- 8
A         EPI         ANNEAL         284         426 0         nd         <0.08         <0.19         nd            A         EPI         ENNEAL         137         68 6         nd         <0.08         <0.19         nd         <0           A         EPI         E1         463         463         nd         <0.08         <0.10         nd         <0           A         EPI         E2         471         236 0         nd         <0.08         <0.07         nd         <0           A         ION         CONSOL         307         480 5         nd         <0.08         <0.01         nd         <0           A         ION         CONSOL         307         480 5         nd         <0.08         <0.01         nd         <0           A         BCKGRD HALL         414         621 0         nd         <0.08         <0.01         nd         <0         <0         <0         <0         <0         <0         <0         <0         <0         <0         <0         <0         <0         <0         <0         <0         <0         <0         <0         <0         <0         <0         <0	8	Q.	딥	SM	840	340				9	Q 05	<b>40 28</b>	
A         EPI         ANNEAL         137         68 6           A         EPI         E1         463         463           A         EPI         E1         463         463           A         EPI         E2         471         236 0           A         EPI         E2         471         236 0           A         ION         CONSOL         307         460 5         nd         <0.08         <0.017         nd           A         BCKGRD HALL         235         379 5         nd         <0.08         <0.17         nd           A         BCKGRD OFFICE         453         679 5         nd         <0.08         <0.12         nd           A         BCKGRD OFFICE         453         226 9         nd         <0.08         <0.12         nd           A         LEC         BH         463         232 0         nd         <0.08         <0.12         nd           A         LEC         KO         435         218 6         nd         <0.08         <0.12         nd           A         LEC         NO         435         223 3         nd         <0.08         <0.12         nd	\$	⋖	굡	ANNEAL	<b>58</b> 7	4260	밑	<0.08	<b>6</b> 0 <b>1 9</b>	5	8 8	60 OV	
A         EPI         E1         463         463           A         EPI         E2         471         2360           A         EPI         E2         471         2360           A         ION         RB         235         3525         nd         <0.08         <0.17         nd         <0.08           A         ION         CONSOL         307         4605         nd         <0.08         <0.17         nd         <0.09         <0.01         nd         <0.09         nd         <0.09         <0.01         nd         <0.09         <0.01         nd         <0.09         <0.01         nd         <0.09	8	∢		ANNEAL	137	989				5	8	<b>\$</b> 0 28	
A         EPI         E2         471         236 0           P         ION         RB         235         352 5         nd         <0 08         <0 23         nd         <0           A         ION         CONSOL         307         460 5         nd         <0 08         <0 17         nd         <0           A         BCKGRD HALL         253         379 5         nd         <0 03         <0 14         nd         <0           A         BCKGRD HALL         253         379 5         nd         <0 03         <0 14         nd         <0           A         BCKGRD OFFICE         453         679 5         nd         <0 08         <0 12         nd         <0           A         BCKGRD OFFICE         453         226 9         nd         <0 08         <0 12         nd         <0           A         LEC         BH         463         232 0         nd         <0 08         <0 12         nd         <0           A         LEC         RO         444         222 3         nd         <0 08         <0 04         nd         <0           A         LEC         PS         444         222 3         nd </td <td>8</td> <td>٧</td> <td>5</td> <td><u>m</u></td> <td>463</td> <td>463</td> <td></td> <td></td> <td></td> <td>þ</td> <td>6 8</td> <td>&amp; &amp;</td> <td></td>	8	٧	5	<u>m</u>	463	463				þ	6 8	& &	
P         ION         RB         235         352.5         nd         <0.08         <0.23         nd         <0.08         <0.07         nd         <0.08         <0.01         nd         <0.08         <0.08         nd         <0.08         <0.08         nd         <0.08         <0.08         <0.08         <0.08         <0.08         <0.08         <0.08         <0.08         <	g	∢		<b>E</b> 2	471	236 0				ā	6 2	<0 17	
A         ION         CONSOL         307         4605         nd         <0.08         <0.17         nd         <0           A         BCKGRD HALL         253         3795         nd         <0.03         <0.14         nd            A         BCKGRD HALL         253         3795         nd         <0.08         <0.14         nd            A         BCKGRD HALL         414         621 0         nd         <0.08         <0.12         nd            A         BCKGRD OFFICE         453         226 9         nd         <0.08         <0.12         nd           P         LEC         BH         463         232 0          <0.08         <0.12         nd           A         LEC         KO         435         218 6         nd         <0.08         <0.74         nd           A         LEC         RO         435         203 2         nd         <0.09         <0.09         nd           A         LEC         PS         444         222 3         nd         <0.09         <0.09         nd           A         LEC         PS         444         666 0         nq	88	۵	Š	RB	235	352.5	þ	<0.08	<0.23	덜	\$ \$	8 ±	
A         BCKGRD HALL         145         2175         nd         <0.03         <0.14         nd         <           A         BCKGRD HALL         253         3795         nd         <0.01         <0.26         nd           A         BCKGRD OFFICE         453         6795         nd         <0.08         <0.12         nq           A         BCKGRD OFFICE         453         226.9          <0.08         <0.12         nq           P         LEC         BH         463         232.0          <0.08         <0.12         nd           P         LEC         RO         435         218.6         nq         0.2         0.74         nd            A         LEC         LOAD R         179         268.5         nq         0.2         0.74         nd            A         LEC         POAD R         179         268.5         nq         0.2         0.74         nd            A         LEC         POAD R         179         89.7         nd            A         LEC         PS         444         222.3          0.42         0.89	8	∢	<u>«</u>	CONSOL	307	4605	2	<0.08	<b>6</b> 17	p	8	80 0 V	
A         BCKGRD HALL         253         3795         nd         <01         <026         nd           A         BCKGRD HALL         414         6210         nd         <018         <013         nq           A         BCKGRD OFFICE         453         6795         nd         <008         <012         nq           A         BCKGRD OFFICE         453         2269         nd         <008         <012         nq           P         LEC         BH         463         2320         nd         <02         074         nd            A         LEC         KO         435         2685         nq         02         074         nd            A         LEC         P3         405         6075         nq         042         069         nq           A         LEC         P5         444         2223         nq         <0         0         0         0         nd            A         LEC         P5         444         2223         nq         <0         0         0         nd            A         LEC         P5         444         6660 <th< td=""><td>23</td><td>∢</td><td>BCKGA</td><td>ID HALL</td><td>145</td><td>217.5</td><td>5</td><td>&lt;0 03</td><td>\$</td><td>5</td><td>&amp; 8</td><td>8 4</td><td></td></th<>	23	∢	BCKGA	ID HALL	145	217.5	5	<0 03	\$	5	& 8	8 4	
A         BCKGRD HALL         414         621 0         nd         <0 08         <0 13         nq           A         BCKGRD OFFICE         453         226 9         nd         <0 08         <0 12         nq           P         LEC         BH         463         226 9         nd         <0 08         <0 12         nq           P         LEC         BH         463         232 0         nd         <0 07         nd         <0 07           A         LEC         KO         435         283 5         nq         0.2         0.74         nd            A         LEC         P3         405         607 5         nq         0.42         0.69         nq           A         LEC         P5         444         222 3         nq         0.02         0.74         nd            A         LEC         P5         444         222 3         nq         <0.08         <0.12         nd           A         LEC         P5         444         222 3         nd         <0.08         <0.12         nd           A         LEC         P5         444         222 3         <0.08         <0.12 <td>8</td> <td>∢</td> <td>BCKGF</td> <td>TO HALL</td> <td>253</td> <td>3795</td> <td>믿</td> <td>6 6</td> <td>92 92 93</td> <td>g</td> <td>8</td> <td>8</td> <td></td>	8	∢	BCKGF	TO HALL	253	3795	믿	6 6	92 92 93	g	8	8	
A         BCKGRD OFFICE         453         6795         nd         <0 08         <0 12         nq           A         BCKGRD OFFICE         453         226 9         nd            P         LEC         BH         463         226 9         nd            P         LEC         BH         463         228 9         nd            A         LEC         KO         435         288 5         nq         0.2         0.74         nd           A         LEC         P3         405         203 2         0.42         0.69         nq           A         LEC         P3         444         222 3         0.42         0.69         nq           A         LEC         P5         444         222 3         0.2         0.30         nd           A         LEC         P5         444         666 0         nq         <0.08         <0.12         nd           A         LEC         P5         444         666 0         nq         <0.08         <0.12         nd           A         LEC         P5         443         664 5         nd         <0.08         <0.12 <t< td=""><td><del>=</del></td><td>4</td><td>BCKGF</td><td>ID HALL</td><td>414</td><td>6210</td><td>Þ</td><td>80 08 √0 08</td><td>6 5</td><td>Ē</td><td>0</td><td>0 16</td><td></td></t<>	<del>=</del>	4	BCKGF	ID HALL	414	6210	Þ	80 08 √0 08	6 5	Ē	0	0 16	
A         BCKGRD OFFICE         453         226 9           P         LEC         BH         463         232 0           P         LEC         KO         435         218 6         nd           A         LEC         LOAD B         179         268 5         nq         0.2         0.74         nd           A         LEC         P3         405         203 2         0.42         0.69         nq           A         LEC         P5         444         222 3         0.42         0.89         nq           A         LEC         P5         444         222 3         nd         0.2         0.30         nd           A         LEC         P5         444         222 3         nq         0.0         0.0         nd           A         LEC         P5         444         666 0         nq         0.2         0.30         nd           A         LEC         P5CP         439         658 5         nd         <0.08         <0.12         nd           A         LEC         P7         443         222 3         nd         <0.08         <0.12         nd           A         LEC<	8	4	<b>BCKGH</b>	OFFICE	453	6795	þ	<0.08	°7 9	ā	90 <b>0</b>	0 12	
P         LEC         BH         463         232 0           P         LEC         KO         435         218 6         nd           A         LEC         LOAD R         179         268 5         nq         0.2         0.74         nd           A         LEC         P3         405         203 2         0.42         0.69         nq           A         LEC         P5         444         22.23         0.42         0.69         nq           A         LEC         P5         444         22.23         nq         0.2         0.30         nd           A         LEC         P5         444         666 0         nq         0.2         0.30         nd           A         LEC         P5         444         666 0         nq         0.2         0.30         nd           A         LEC         P5         444         666 0         nq         0.02         0.30         nd           A         LEC         P5CP         439         658 5         nd          nd           A         LEC         P7         443         222 3         nd           nd <td>5</td> <td>∢</td> <td>BCKGH</td> <td>ID OFFICE</td> <td>453</td> <td>2269</td> <td></td> <td></td> <td></td> <td>5</td> <td>00 B</td> <td>0 18</td> <td></td>	5	∢	BCKGH	ID OFFICE	453	2269				5	00 B	0 18	
P         LEC         KO         435         218 6         nd         nd         nd           A         LEC         LOAD R         179         268 5         nq         0.2         0.74         nd           A         LEC         P3         405         203 2         0.42         0.69         nq           A         LEC         P5         444         222 3         0.42         0.69         nq           A         LEC         P5         444         666 0         nq         0.2         0.30         nd           A         LEC         P5         444         666 0         nq         0.2         0.30         nd           A         LEC         P5         444         666 0         nq         0.2         0.30         nd           A         LEC         P5CP         439         658 5         nd         <0.08         <0.12         nd           A         LEC         P7         443         654 5         nd         <0.08         <0.12         nd           A         LEC         P7         443         222 3         nd         <0.08         <0.12         nd	8	۵	E	H	463	232 0					0 56	2 41	1.27
A         LEC         LOAD R         179         268 5         nq         0.2         0.74         nd           A         LEC         P3         405         203 2         nd         nd           A         LEC         P3         405         607 5         0.42         0.69         nq           A         LEC         P5         444         222 3         nd         nd         nd           A         LEC         P6CP         439         219 9         nd         nd         nd           A         LEC         P5CP         439         658 5         nd         <0.08         <0.12         nd           A         LEC         P7         443         664 5         nd         <0.08         <0.12         nd           A         LEC         P7         443         664 5         nd         <0.08         <0.12         nd           A         LEC         P7         443         222 3         nd         <0.08         <0.12         nd	ଷ	۵	Ë	õ	435	2186				돧	\$ \$	& 50 81	
A         LEC         LOAD B         179         89 7         nd           A         LEC         P3         405         203 2         nd         nd           A         LEC         P5         444         222 3         nd         nd         nd           A         LEC         P5CP         439         219 9         nd         nd         nd           A         LEC         P5CP         439         658 5         nd         <0.08         <0.12         nd           A         LEC         P7         443         664 5         nd         <0.08         <0.12         nd           A         LEC         P7         443         664 5         nd         <0.08         <0.12         nd	ξ.	∢	E	LOAD R	179	268 5	ā	0.2	0 74	덛	\$ 8	& 5	
A         LEC         P3         405         2032           A         LEC         P5         444         2223         0.42         0.69         nq           A         LEC         P5         444         2223         nq         0.2         0.80         nd           A         LEC         P5CP         439         219.9         nd         A         LC         nd           A         LEC         P7         443         664.5         nd         <0.08         <0.12         nd           A         LEC         P7         443         222.3         nd         <0.08         <0.12         nd	$\aleph$	∢	Ë	LOAD B	179	89 7				pu	6 8	<0.45	
A         LEC         P3         405         607 5         0 42         0 69         nq           A         LEC         P5         444         222 3         nd         nd         nd         nd         nd           A         LEC         P5CP         439         658 5         nd         <0.08         <0.12         nd           A         LEC         P7         443         664 5         nd         <0.08         <0.12         nd           A         LEC         P7         443         222 3         nd         <0.08         <0.12         nd	33	⋖	CEC	P3	405	203 2				멑	\$ \$	9 9 9	
A         LEC         P5         444         222.3         nd           A         LEC         P5CP         434         666.0         nq         0.2         0.30         nd           A         LEC         P5CP         439         658.5         nd         <0.08         <0.12         nd           A         LEC         P7         443         664.5         nd         <0.08         <0.12         nd           A         LEC         P7         443         222.3         nd         <0.08         <0.12         nd	8	∢	CEC	P3	405	607 5		0 42	0 69	ğ	0	990	0 95
A LEC P5 444 6660 nq 0.2 0.30 nd A LEC P6CP 439 219.9 A LEC P5CP 439 658.5 nd <0.08 <0.12 nd A LEC P7 443 664.5 nd <0.08 <0.12 nd A LEC P7 443 222.3	8	4	Ë	<b>5</b>	444	222 3				돧	ଟ ୧୨	8	
A LEC P6CP 439 219 9  A LEC P5CP 439 658 5 nd <0.08 <0.12 nd  A LEC P7 443 6645 nd <0.08 <0.12 nd  A LEC P7 443 222 3	R	∢	띮	ξ.	4	0 999	탇	0 5	99	ē	60 8	8 8	
A LEC P5CP 439 6585 nd <0.08 <0.12 nd A LEC P7 443 6645 nd <0.08 <0.12 nd A LEC P7 443 2223	2	<	LEC	PSCP	439	2199				ď	\$ \$	& 35	
A LEC P7 443 6645 nd <0,08 <0,12 nd A LEC P7 443 2223	88	∢	LEC	P5CP	439	658 5	ā	<0.08	<b>0</b>	달	0 \$	8	
A LEC P7 443 2223	27	<	S	Р7	443	664 5	ğ	<0 08 <0 08	<0 12	멑	۸ 2	% %	
	98	⋖	Ë	P7	443	222 3				пd	<0.04	<0 18	

Table A-3 - Continued

:	Sample			Person/	Time	Volume	Det.	Arsenic	Arsenic	Det St	Gallium	Gallium	Ratio
Date	Number Type	Type	Room	Loca-	(Min.)	(inters)	timit.	mass	0000	Limit	mass	Cond	Gallium/
				tion				(6n)	(£m/6n)		(Bn)	(ng/m3)	Arsenic
06/18/87	5151	٩	CLEC	AW	175	878	:				0.87	991	0 08
06/18/87	5136	*	CEC	Ē	8	2700		23	100 00		<b>8</b>	17 78	0 18
06/18/87		<	CLEC	፻	180	93.5					12	12.84	0 12
06/18/87		∢	CLEC	P1CP	228	114 2				5	8	<b>△</b> 73	
06/18/87		∢	CLEC	P1CP	228	3420	멑	00	& ₽	g	% 9	8 0 28 0 28	
06/18/87		<	es	GS1	371	609 4		6 62	477		<u>۳</u>	5 09	1 07
06/18/87		4	SS	682	450	225.4					0 36	1 60	1 06
06/18/87		∢	GS	685	300	525 0		3.7	7.08		99	7 43	1 05
06/18/87		Δ,	<u>G</u>	SW	356	35.6				5	8 8 8	\$ \$	
78/18/87		4	급	Ш	452	45.2				5	00 00 00 00 00 00 00 00 00 00 00 00 00	8 4	
06/18/87	5029	∢	<u>.</u>	A EPI E2	454	227 5				2	Q 00 05	8 0 0 0 0 0 0 0	
06/18/87		∢	<u>~</u>	ANNEAL	373	186 7				ם	8 9 9	<b>6</b>	
06/18/87		Δ.	<u>N</u>	HB	286	429 0	p	0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0	<b>~0 0</b>	ē	% %	\$ 8	
06/18/87		⋖	<u>8</u>	CONSOL	453	679.5	ā	<0.03	\$ \$	Þ	8 8	<b>⇔</b>	
06/18/87		4	BCKGR	D HALL	455	46.5				5	40 02 40 02	8 4	
78/11/87		*	BCKGH	D HALL	234	3510	믿	6	% √0 78	5	\$ \$	<0.27	
06/18/87		∢	BCKGR	D HALL	246	3690	DC.	<0.08	<b>6</b> 25	g	8	8	
06/18/87		4	BCKGA	D OFFICE	444	222 4				ទ	0	0 45	
06/18/87		4	BCKGH	D OFFICE	450	675 0		0 3	4		031	0.46	1 03

Table A-4 Acid Sample Resutts

	Sample						HCL	HCL	Nitric	Nitric
Date	Number	Media	Type	Room	Time	Volume	mase	Ş	mass	Ç
					(mm)	(liters)	(Bn)	(cm/gu)	(50)	(u <i>gi</i> /m3)
06/15/87	910	Υ	∢	Ü	128	\$	ß	78	90	13
06/15/87	813	ΑŢ	∢	SH.	88	103	ιô	49	<b>40.5</b>	Ŷ
06/15/87	803	ΑT	∢	<u></u>	ង	<del>1</del> 8	⊽	♡	<0.5	4
06/16/87	118	ΑT	∢	LEC	212	106	5	142	43	4
06/16/87	812	¥Τ	∢	LEC	243	121	1520	12600	839	6920
06/16/87	824	ΑT	∢	굡	<del>2</del>	83	CVI	8	<0.5	ψ.
06/16/87	820	ΑT	⋖	굡	ଷ୍ଟ	<u>6</u>	-	5	<b>₹</b> 02	٧
06/17/87	805	ΑT	∢	LEC	155	<b>8</b> 2	ო	ස	<b>0 0 0 0</b>	Ÿ
06/17/87	80 <del>1</del>	ΑT	4	LEC	31	156	73	47	16	유
06/17/87	823	ΑŢ	4	<u>.</u>	245	52	⊽	80	<0.5	<b>^</b>
06/17/87		ΑT	*	딥	212	106	٧	♡	<b>0</b> 20	٧
06/18/87		AT	∢	S S	88 780	130	131	1008	8	- 69
06/18/87		ΑT	∢	LEC	\$	67	5	569	හ භ	4
06/18/87	8 <u>2</u> 5	ΑT	4	딦	241	120	က	ક્ષ	<b>⇔</b>	\$
06/18/87	828	AT	∢	딦	192	<b>9</b> 8	7	×10	<0.5	\$
06/15/87	814	AT		Blank		0	ĸ		<0.5	
06/16/87	_	ΑŢ		Blank		0	מו		<b>0</b> 5	
06/11/87	88	ΑŢ		Blank		0	5		8	
06/17/87	-	ΑT		Blank		0	9		<0.5 5	
06/18/87		ΑT		Blank		0	8		^ 60.5	
06/18/87	•	ΑT		Blank		٥	7		<b>0</b>	